

# TPS1685x 9V–80V, 3.5mΩ, 20A Stackable Integrated Hotswap (eFuse) With Accurate and Fast Current Monitor

## 1 Features

- Input operating voltage range: 9V to 80V
  - 92V absolute maximum
  - Withstands negative voltages up to –5V at output
- Integrated FET with low on-resistance:  $R_{ON} = 3.5\text{m}\Omega$  (typ)
- Active high enable input with adjustable undervoltage lockout (UVLO)
- Adjustable overvoltage protection
- Supports parallel connection of multiple eFuses with device state synchronization and current sharing
- Adjustable output slew rate control ( $dVdt$ ) for inrush current protection
- Precise load current monitoring
  - <3% error for over 50-100% of max current
  - 1MHz bandwidth
- Robust overcurrent protection
  - Circuit-breaker response
  - Adjustable threshold: 2A to 20A
  - Overcurrent protection accuracy:  $\pm 3\%$
  - Adjustable transient overcurrent timer (ITIMER) to support peak currents
- Fast-trip response to short-circuit events
- Overtemperature protection (OTP) with analog die temperature monitor output (TEMP)
  - FET SOA:  $0.7\text{W}\sqrt{\text{s}}$
- FET health monitoring and reporting
- Fault indication pin (FLT)
- Power Good indication pin (PGOOD)
- Small footprint: QFN 6mm × 5mm
  - IPC9592B clearance for 60V

## 2 Applications

- Input hotswap and hotplug
- [Server and high performance computing](#)
- [Network interface cards](#)
- [Graphics and hardware accelerator cards](#)
- [Data center switches and routers](#)
- [Fire alarm control panel](#)

## 3 Description

The TPS1685x is an integrated high current circuit protection and power management device. The device provides multiple protection modes using very few external components and is a robust defense against overloads, short-circuits and excessive inrush current. Applications with particular inrush current requirements can set the output slew rate with a single external capacitor. Output current limit level can be set by user as per system needs. A user adjustable overcurrent blanking timer allows systems to support transient peaks in the load current without tripping the eFuse. An integrated fast and accurate sense analog load current monitor facilitates predictive maintenance and advanced dynamic platform power management such as Intel® PSYS and PROCHOT# to optimize server and data-center performance.

Multiple TPS1685x devices can be connected in parallel to increase the total current capacity for high power systems. All devices actively synchronize the operating state and share current during start-up as well as steady state to avoid over-stressing some of the devices which can result in premature or partial shutdown of the parallel chain.

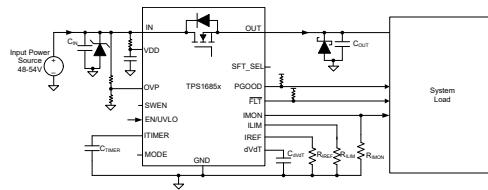
The devices are characterized for operation over a junction temperature range of  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ .

### Package Information

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
TPS16850VMAR		
TPS16851VMAR		
TPS16850AVMAR	VMA (LQFN, 23)	6.00mm × 5.00mm
TPS16851AVMAR		

(1) For all available packages, see [Section 11](#).

(2) The package size (length × width) is a nominal value and includes pins, where applicable.



**Simplified Schematic**



An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. PRODUCTION DATA.

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## 4 Device Comparison Table

PART NUMBER	FAULT BEHAVIOR	Fixed Fast Trip Threshold (FFT)
TPS16850	Auto-retry	73A
TPS16851	Latch-off	73A
TPS16850A	Auto-retry	83A
TPS16851A	Latch-off	83A

## 5 Pin Configuration and Functions

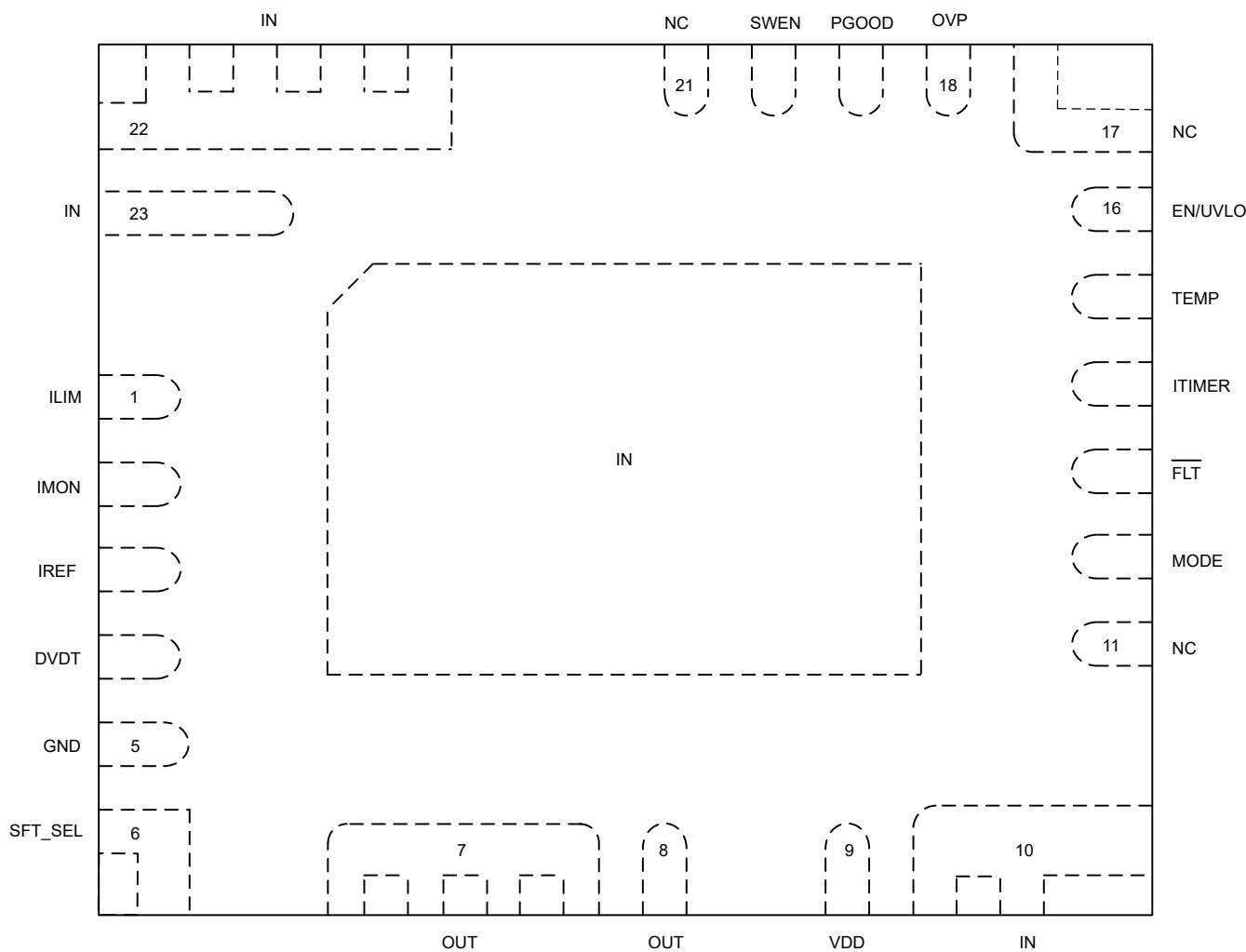


Figure 5-1. TPS1685x VMA Package, QFN 23-Pin (Top View)

Table 5-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
ILIM	1	I/O	An external resistor from this pin to GND sets the active current sharing threshold during steady-state. This pin also serves as individual eFuse current monitor output during steady state. <i>Do not leave floating.</i>
IMON	2	I/O	An external resistor from this pin to GND sets the overcurrent protection threshold and fast-trip threshold during steady-state. This pin also acts as a fast and accurate analog output load current monitor signal during steady-state. <i>Do not leave floating.</i>
IREF	3	I/O	This pin sets the reference voltage for overcurrent, short-circuit protection and active current sharing blocks. The reference voltage can be generated using internal current source and resistor on this pin, or can be driven from external voltage source. <i>Do not leave floating.</i>
dVdT	4	I/O	This pin is used to configure the output slew rate during Start-up. Leave this pin open to allow fastest start-up. Connect capacitor to ground to slow down the slew rate to manage inrush current.
GND	5	G	Device ground reference pin. Connect to system ground.

**Table 5-1. Pin Functions (continued)**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
SFT_SEL	6	I/O	This pin selects the scalable fast-trip threshold multiplier during steady state. Connect a resistor from this pin to GND to select the fast-trip threshold multiplier.
OUT	7, 8	P	Power output. Must be soldered to the output power plane uniformly for proper heat dissipation.
VDD	9	P	Controller power input pin. Can be used to power the internal control circuitry with a filtered and stable supply which is not affected by system transients. Connect this pin to VIN through a series resistor and add a decoupling capacitor to GND.
IN	10, 22, 23	P	Power input. Must be soldered to the input power plane uniformly for proper heat dissipation.
NC	11, 17, 21	—	Do not connect anything to this pin.
MODE	12	I	This pin is used to configure the device for standalone/primary or secondary mode. Connect the pin to GND to configure device as a secondary to a primary eFuse/controller. Leave the pin floating for standalone/primary mode of operation.
FLT	13	O	This is an open drain active low pin which is pulled low to indicate a fault. Pull up this pin to external supply voltage with a resistor.
ITIMER	14	I/O	A capacitor from this pin to GND sets the overcurrent blanking interval during which the output current can temporarily exceed the overcurrent threshold (but lower than fast-trip threshold) during steady-state operation before the device overcurrent response takes action.
TEMP	15	I/O	Analog voltage output for junction temperature. Can be tied together with TEMP outputs of multiple devices in a parallel configuration to indicate the peak temperature of the parallel chain.
EN/UVLO	16	I	Active high enable input. Connect resistor divider from input supply to set the undervoltage threshold. Do not leave floating.
OVP	18	I	This pin can be used to set the over-voltage set-point. Connect a resistor divider from VIN to this pin. Do not leave floating.
PGOOD	19	O	This is an open-drain active high power good pin which is asserted high when the device is in steady state. This pin has a weak internal pull-up to internal supply voltage.
SWEN	20	I/O	This is an open-drain signal to indicate and control power switch ON/OFF status. This pin facilitates active synchronization between multiple devices in a parallel chain. This pin has a weak internal pull-up to internal supply voltage.
IN	PowerPad	P	Power input. Must be soldered to the input power plane uniformly for proper heat dissipation.

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

Parameter	Pin	MIN	MAX	UNIT
$V_{INMAX}, V_{DDMAX}$	IN, VDD	-0.3	90	V
$V_{INMAX,25}, V_{DDMAX,25}$	IN, VDD	-0.3	92	V
$V_{OUTMAX}$	OUT	-5 <sup>(2)</sup>	Min(92 V, $V_{IN} + 0.3$ )	
$V_{IN} - V_{OUT}$	IN, OUT	-0.3	90	V
$V_{ILIMMAX}$	ILIM	-0.3	6	V
$V_{IMONMAX}$	IMON	-0.3	6	V
$V_{SFT\_SELMAX}$	SFT_SEL	-0.3	6	V
$V_{OVP}$	OVP	-0.3	6	V
$V_{ITIMER}$	ITIMER	-0.3	6	V
$V_{IREFMAX}$	IREF	-0.3	6	V
$V_{DVDTMAX}$	DVDT	-0.3	6	V
$V_{MODEMAX}$	MODE	-0.3	6	V
$V_{SWENMAX}$	SWEN	-0.3	6	V
$I_{SWENMAX}$	SWEN		10	mA
$V_{ENMAX}$	EN/UVLO	-0.3	6	V
$V_{FLTMAX}$	FLT	-0.3	6	V
$I_{FLTMAX}$	FLT		10	mA
$V_{PGOODMAX}$	PGOOD	-0.3	6	V
$I_{PGOODMAX}$	PGOOD		10	mA
$V_{TEMP}$	TEMP	-0.3	6	V
$I_{MAX}$	IN to OUT	Internally Limited		A
$T_{JMAX}$		Internally Limited		°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

(2) During FET OFF condition for negative transients.

### 6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	$\pm 1500$
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	$\pm 500$

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

Parameter	Pin	MIN	MAX	UNIT
$V_{IN}$	Input Voltage Range	IN	9	80
$V_{DD}$	Supply Voltage Range	VDD	9	80
$V_{OUT}$	Output Voltage Range	OUT		$V_{IN}$
$V_{EN/UVLO}$	Enable Pin Voltage Range	EN/ UVLO		5
$dVdT$	$dVdT$ Pin Cap Voltage Rating	$dVdT$	4	V
$V_{PGOOD}$	PGOOD Pin Pull-up Voltage Range	PGOOD	5	V
$V_{FLT}$	FLT Pin Pull-up Voltage Range	FLT	5	V
$V_{SWEN}$	SWEN Pin Pull-up Voltage Range	SWEN	5	V
$V_{TEMP}$	TEMP Pin Voltage Rating	TEMP	5	V
$V_{IREF}$	IREF Pin Voltage Range	IREF	0.3	1.2
$V_{ILIM}$	ILIM Pin Voltage Range	ILIM		0.4
$V_{IMON}$	IMON Pin Voltage Range	IMON		1.2
$C_{IN}$	Capacitance on IN pins	IN	10	nF
$C_{OUT}$	Capacitance on OUT pins	OUT	10	$\mu$ F
$dV_{IN}/dt$	Slew rate on IN pins	IN		500 V/ $\mu$ s
$I_{MAX}$	RMS Switch Current $T_J \leq 125^\circ\text{C}$	IN to OUT	20	A
$I_{MAX, \text{Pulse}}$	Peak Output Current for $\leq 10$ ms duration, $T_A \leq 70^\circ\text{C}$	IN to OUT	27	A
$T_J$	Junction temperature		-40	125
				$^\circ\text{C}$

## 6.4 Thermal Information

THERMAL METRIC <sup>(1) (2)</sup>		TPS1685x	UNIT
		LQFN	
		PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	22.1	$^\circ\text{C}/\text{W}$
$\Psi_{JT}$	Junction-to-top characterization parameter	1.1	$^\circ\text{C}/\text{W}$
$\Psi_{JB}$	Junction-to-board characterization parameter	9.4	$^\circ\text{C}/\text{W}$

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.

(2) Based on simulations conducted with the device mounted on a "3 x 4.5" PCB (2s2p) as JESD51-7

## 6.5 Electrical Characteristics

$-40^\circ\text{C} \leq T_J \leq +125^\circ\text{C}$ ,  $V_{IN} = V_{DD} = 50\text{V}$ , OUT = Open,  $R_{ILIM} = 931\text{k}\Omega$ ,  $R_{IMON} = 2.55\text{k}\Omega$ ,  $V_{IREF} = 1\text{V}$ ,  $\bar{FLT} = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $PGOOD = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $C_{OUT} = 10\text{\mu F}$ ,  $C_{IN} = 10\text{nF}$ ,  $dVdT = \text{Open}$ ,  $ITIMER = \text{Open}$ ,  $V_{EN/UVLO} = 2\text{V}$ ,  $TEMP = \text{Open}$ ,  $MODE = \text{Open}$ . (All voltages referenced to GND, (unless otherwise noted))

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>INPUT SUPPLY (VDD)</b>						
$V_{IN}$	Input voltage range		9	80		V
$V_{DD}$	Input voltage range		$V_{IN}$	80		V
$I_{QON(VDD)}$	$V_{DD}$ ON state quiescent current	$V_{DD} > V_{UVPR}$ , $V_{EN} \geq V_{UVLOR}$ , $V_{OVP} < V_{OVPF}$		0.6	4	mA
$V_{UVPR}$	$V_{DD}$ Undervoltage Protection Threshold Rising	$V_{DD}$ Rising		8.5	8.9	V
$V_{OVPF}$	$V_{DD}$ Undervoltage Protection Threshold falling	$V_{DD}$ Falling	6.7	7.05		V
$V_{UVPHYS}$	UVPHYS Hysteresis VDD			1.5		V
<b>INPUT SUPPLY (IN)</b>						
$V_{UVPR(VIN)}$	VIN Undervoltage Protection Threshold	$V_{IN}$ Rising		8.45	9	V
$V_{OVPF(VIN)}$	VIN Undervoltage Protection Threshold	$V_{IN}$ Falling	6.5	7.05		V
$I_{QON(VIN)}$	$V_{IN}$ ON state quiescent current	$V_{EN} \geq V_{UVLOR}$		1.69		mA
$I_{QOFF(VIN)}$	$V_{IN}$ OFF state current	$V_{SDR} < V_{EN} < V_{UVLO}$		47		$\mu\text{A}$
$I_{SD(VIN)}$	$V_{IN}$ shutdown current	$V_{EN} < V_{SDF}$		46		$\mu\text{A}$
<b>ENABLE / UNDERRVOLTAGE LOCKOUT (EN/UVLO)</b>						
$V_{UVLO(R)}$	EN/UVLO pin voltage threshold for turning on, rising	EN/UVLO Rising	1.18	1.21	1.23	V
$V_{UVLO(F)}$	EN/UVLO pin voltage threshold for turning off and engaging QOD, falling (primary device)	EN/UVLO Falling	1	1.12	1.14	V
$V_{UVLOF}$	EN/UVLO pin voltage threshold for turning off and engaging QOD, falling (Secondary device)	EN/UVLO Falling		1		V
$V_{UVLOHYS}$	UVLO Hysteresis			89		$\text{mV}$
$V_{SDF}$	Shutdown threshold	EN/UVLO Falling	0.4	0.42		V
$V_{SDR}$	Shutdown threshold	EN/UVLO Rising		0.5	0.55	V
$I_{ENLKG}$	EN/UVLO pin leakage current		-100		100	nA
<b>OVERVOLTAGE PROTECTION (IN)</b>						
$V_{OVP(R)}$	Overvoltage protection threshold (rising)	OVP pin rising	1.11	1.17	1.20	V
$V_{OVP(F)}$	Overvoltage protection threshold (falling)	OVP pin falling	1.08	1.12	1.15	V
$V_{OVPHYS}$	Overvoltage protection threshold (Hysteresis)			57		$\text{mV}$
$I_{OVPPLKG}$	OVP pin leakage current	$V_{OVP} = 1.2\text{V}$	-100		100	nA
$V_{OVPR(IN)}$	Internal Overvoltage protection threshold (rising)	$V_{IN}$ Rising	84	90.8	95	V
$V_{OVPF(IN)}$	Internal Overvoltage protection threshold (falling)	$V_{IN}$ falling	77	84.5	90	V
<b>ON-RESISTANCE (IN - OUT)</b>						
$R_{ON}$	ON state resistance	$I_{OUT} = 12\text{A}$ ; $T_J = 25^\circ\text{C}$		3.5	5.55	$\text{m}\Omega$
$R_{ON}$	ON state resistance	$I_{OUT} = 12\text{A}$ ; $T_J = -40^\circ\text{C}$ to $125^\circ\text{C}$			6.1	$\text{m}\Omega$
<b>CURRENT LIMIT REFERENCE (IREF)</b>						
$V_{IREF}$	IREF pin recommended voltage range			0.3	1.2	V
$I_{IREF}$	IREF internal sourcing current	$V_{IREF} = 1\text{V}$	24.2	25	25.8	$\mu\text{A}$

## 6.5 Electrical Characteristics (continued)

$-40^\circ\text{C} \leq T_J \leq +125^\circ\text{C}$ ,  $V_{\text{IN}} = V_{\text{DD}} = 50\text{V}$ ,  $\text{OUT} = \text{Open}$ ,  $R_{\text{ILIM}} = 931\Omega$ ,  $R_{\text{IMON}} = 2.55\text{k}\Omega$ ,  $V_{\text{IREF}} = 1\text{V}$ ,  $\text{FLT} = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $\text{PGOOD} = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $C_{\text{OUT}} = 10\mu\text{F}$ ,  $C_{\text{IN}} = 10\text{nF}$ ,  $\text{dVdT} = \text{Open}$ ,  $\text{ITIMER} = \text{Open}$ ,  $V_{\text{EN/UVLO}} = 2\text{V}$ ,  $\text{TEMP} = \text{Open}$ ,  $\text{MODE} = \text{Open}$ . (All voltages referenced to GND, (unless otherwise noted))

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>CURRENT LIMIT (ILIM)</b>						
$G_{\text{ILIM(LIN)}}$	Current Monitor Gain (ILIM:IOUT) vs. IOUT.	Device in steady state (PG asserted), $I_{\text{OUT}} = 12\text{ A}$	17	18	20.6	$\mu\text{A/A}$
$I_{\text{start-up peak}}$	Peak Current at Startup (Ipeak )	$V_{\text{OUT}} > V_{\text{FB}}$ , GHI deasserted. $V_{\text{IN}} \leq 60\text{V}$		0.5		A
$V_{\text{FB}}$	Foldback voltage			2		V
<b>OUTPUT CURRENT MONITOR AND OVERCURRENT PROTECTION (IMON)</b>						
$G_{\text{IMON}}$	Current Monitor Gain (IMON:IOUT)	Device in steady state (PG asserted), for $12\text{A} \leq I_{\text{OUT}} \leq 20\text{A}$	17.7	18.18	18.49	$\mu\text{A/A}$
$G_{\text{IMON}}$	Current Monitor Gain (IMON:IOUT)	Device in steady state (PG asserted), $I_{\text{OUT}} = 4\text{A}$	17.4	18.31	19.1	$\mu\text{A/A}$
$I_{\text{OCP}}$	IOUT Current limit trip (Circuit-Breaker) threshold	$R_{\text{IMON}} = 2.55\text{k}\Omega$ , $V_{\text{IREF}} = 1\text{V}$	21.2	21.7	22.3	A
<b>CURRENT FAULT TIMER (ITIMER)</b>						
$I_{\text{ITMR}}$	ITIMER pin internal discharge current	$I_{\text{OUT}} > I_{\text{OCP}}$ , ITIMER $\downarrow$	1.77	2.2	2.6	$\mu\text{A}$
$R_{\text{ITMR}}$	ITIMER pin internal pull-up resistance		5	12.3	23	$\text{k}\Omega$
$V_{\text{INT}}$	ITIMER pin internal pull-up voltage	$I_{\text{OUT}} < I_{\text{OCP}}$	4.4	5	5.6	V
$\Delta V_{\text{ITMR}}$	ITIMER discharge voltage	$I_{\text{OUT}} > I_{\text{TRIP}}$ , ITIMER $\downarrow$	1.28	1.5	1.8	V
$\Delta V_{\text{ITMR}}/I_{\text{ITMR}}$	ITIMER Discharge voltage to Discharge current ratio	$I_{\text{OUT}} > I_{\text{TRIP}}$ , ITIMER $\downarrow$	0.49	0.72	0.97	$\text{V}/\mu\text{A}$
<b>SHORT-CIRCUIT PROTECTION</b>						
$I_{\text{FFT}}$	Fixed fast-trip threshold in steady state (primary)(TPS1685xA only)	PG asserted High (MODE = Open)		83		A
$I_{\text{FFT}}$	Fixed fast-trip threshold in steady state (primary)(TPS1685x)	PG asserted High (MODE = Open)		73		A
$I_{\text{FFT}}$	Fixed fast-trip threshold in steady state (primary)(TPS1685xA only)	PG asserted High (MODE = Open); $T_J = 25^\circ\text{C}$ to $125^\circ\text{C}$	65			A
$I_{\text{FFT}}$	Fixed fast-trip threshold in steady state (primary)(TPS1685x)	PG asserted High (MODE = Open); $T_J = 25^\circ\text{C}$ to $125^\circ\text{C}$	55			A
$I_{\text{FFT}}$	Fixed fast trip threshold in steady state (secondary)(TPS1685A0 only)	PG asserted High (MODE = GND)		105		A
$I_{\text{FFT}}$	Fixed fast trip threshold in steady state (secondary)(TPS1685x)	PG asserted High (MODE = GND)		95		A
$I_{\text{SFT}}$	Scalable fast trip current	$R_{\text{SFT\_SEL}} < 95\text{k}\Omega$ , PG asserted High (MODE = Open)		38.3		A
$I_{\text{SFT}}$	Scalable fast trip current	$105\text{k}\Omega < R_{\text{SFT\_SEL}} < 195\text{k}\Omega$ , PG asserted High (MODE = Open)		$2.5 \times I_{\text{OCP}}$		A
$I_{\text{SFT}}$	Scalable fast trip current	$105\text{k}\Omega < R_{\text{SFT\_SEL}} < 195\text{k}\Omega$ , PG asserted High (MODE = GND)		$2.8 \times I_{\text{OCP}}$		A
$I_{\text{SFT}}$	Scalable fast trip current	$205\text{k}\Omega < R_{\text{SFT\_SEL}} < 295\text{k}\Omega$ , PG asserted High (MODE = Open)		$2 \times I_{\text{OCP}}$		A
$I_{\text{SFT}}$	Scalable fast trip current	$205\text{k}\Omega < R_{\text{SFT\_SEL}} < 295\text{k}\Omega$ , PG asserted High (MODE = GND)		$2.26 \times I_{\text{OCP}}$		A

## 6.5 Electrical Characteristics (continued)

$-40^\circ\text{C} \leq T_J \leq +125^\circ\text{C}$ ,  $V_{\text{IN}} = V_{\text{DD}} = 50\text{V}$ ,  $\text{OUT} = \text{Open}$ ,  $R_{\text{ILIM}} = 931\Omega$ ,  $R_{\text{IMON}} = 2.55\text{k}\Omega$ ,  $V_{\text{IREF}} = 1\text{V}$ ,  $\overline{\text{FLT}} = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $\text{PGOOD} = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $C_{\text{OUT}} = 10\mu\text{F}$ ,  $C_{\text{IN}} = 10\text{nF}$ ,  $\text{dVdT} = \text{Open}$ ,  $\text{ITIMER} = \text{Open}$ ,  $V_{\text{EN/UVLO}} = 2\text{V}$ ,  $\text{TEMP} = \text{Open}$ ,  $\text{MODE} = \text{Open}$ . (All voltages referenced to GND, (unless otherwise noted))

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_{\text{SFT}}$	Scalable fast trip current	$305\text{k}\Omega < R_{\text{SFT\_SEL}}$ , PG asserted High (MODE = Open)		$1.5 \times I_{\text{OCP}}$		A
$I_{\text{SFT}}$	Scalable fast trip current	$305\text{k}\Omega < R_{\text{SFT\_SEL}}$ , PG asserted High (MODE = GND)		$1.71 \times I_{\text{OCP}}$		A
$I_{\text{SFT(SAT)}}$	Scalable fast trip Current (inrush)	During Powerup, PGOOD Low		2		A
<b>ACTIVE CURRENT SHARING</b>						
$R_{\text{ON(ACS)}}$	$R_{\text{ON}}$ during Active current sharing	$V_{\text{ILIM}} > 1.1 \times (1/3) \times V_{\text{IREF}}$	4.38	6.9		$\text{m}\Omega$
$G_{\text{IMON(ACS)}}$	$\text{IMON:IOUT}$ ratio during active current limiting	PG asserted High, $V_{\text{ILIM}} > 1.1 \times V_{\text{IREF}}$	17.24	18.49	19.84	$\mu\text{A}/\text{A}$
$CL_{\text{REF(ACS)}}$	Ratio of active current sharing trigger threshold to steady state circuit-breaker threshold	PG asserted High		36.67		%
<b>INRUSH CURRENT PROTECTION (DVDT)</b>						
$I_{\text{DVDT}}$	dVdt Pin Charging Current (Primary/Standalone mode)	MODE = Open	1.5	2.0	3	$\mu\text{A}$
$G_{\text{DVDT}}$	dVdt Gain	$0.4\text{V} < V_{\text{dVdt}} < 2.4\text{V}$	22	25	28	V/V
$I_{\text{DVDTLKG}}$	dVdt Pin Leakage Current (Secondary mode)	MODE = GND	-100		100	nA
$R_{\text{DVDT}}$	dVdt Pin to GND Discharge Resistance			500		$\Omega$
<b>GHI</b>						
$V_{\text{GS(GHI) Rising}}$	G-S Threshold when GHI/PG is asserted			7		V
$R_{\text{ON(GHI)}}$	$R_{\text{ON}}$ When GHI/PG is asserted			3.8		$\text{m}\Omega$
<b>QUICK OUTPUT DISCHARGE (QOD)</b>						
$I_{\text{QOD}}$	Quick Output Discharge pull-down current	$V_{\text{SD(R)}} < V_{\text{EN}} < V_{\text{UVLO}}$ , $-40 < T_J < 125^\circ\text{C}$	17	22	25	mA
<b>TEMPERATURE SENSOR OUTPUT (TEMP)</b>						
$G_{\text{TEMP}}$	TEMP sensor gain	$V_{\text{IN}} = 51\text{V}$	2.6	2.73	3.1	$\text{mV}/^\circ\text{C}$
$V_{\text{TEMP}}$	TEMP pin output voltage	$T_J = 25^\circ\text{C}$ , $V_{\text{IN}} = 51\text{V}$	670	678	690	$\text{mV}$
$I_{\text{TMPSRC}}$	TEMP pin sourcing current	$V_{\text{IN}} = 51\text{V}$	110	119	133	$\mu\text{A}$
$I_{\text{TMPSNK}}$	TEMP pin sinking current	$V_{\text{IN}} = 51\text{V}$	8	10	14	$\mu\text{A}$
<b>OVERTEMPERATURE PROTECTION (OTP)</b>						
$T_{\text{SD}}$	Absolute Thermal Shutdown Rising Threshold	$T_J$ Rising, $V_{\text{IN}} = 51\text{V}$		150		$^\circ\text{C}$
$T_{\text{SDHYS}}$	Absolute Thermal shutdown hysteresis	$T_J$ Falling, $V_{\text{IN}} = 51\text{V}$		13		$^\circ\text{C}$
<b>FET HEALTH MONITOR</b>						
$V_{\text{DSFLT}}$	FET D-S Fault Threshold	$\text{SWEN} = \text{L}$ , $V_{\text{IN}} = 51\text{V}$		0.5		V
$V_{\text{DSOK}}$	FET D-S Fault Recovery Threshold	$\text{SWEN} = \text{L}$ , $V_{\text{IN}} = 51\text{V}$		0.64		V
<b>SINGLE POINT FAILURE (IMON, IREF, ITIMER)</b>						
$I_{\text{OC_BKP}}$	Back-up overcurrent protection threshold	IMON short to GND		38.3		A

## 6.6 Logic Interface

$-40^\circ\text{C} \leq T_J \leq +125^\circ\text{C}$ ,  $V_{IN} = V_{DD} = 45\text{V}$  to  $60\text{V}$ ,  $OUT = \text{Open}$ ,  $R_{ILIM} = 931\Omega$ ,  $R_{IMON} = 2.55\text{k}\Omega$ ,  $V_{IREF} = 1\text{V}$ ,  $\overline{FLT} = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $PGOOD = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $C_{OUT} = 10\mu\text{F}$ ,  $C_{IN} = 10\text{nF}$ ,  $dVdT = \text{Open}$ ,  $ITIMER = \text{Open}$ ,  $V_{EN/UVLO} = 2\text{V}$ ,  $TEMP = \text{Open}$ ,  $MODE = \text{Open}$ . (All voltages referenced to GND, (unless otherwise noted))

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SWEN</b>						
$R_{SWEN}$	SWEN pin pull-down resistance	SWEN de-asserted Low	6.8			$\Omega$
<b>FAULT INDICATION (FLT)</b>						
$R_{FLTB}$	FLT pin pull-down resistance	FLT asserted Low	6.6			$\Omega$
$I_{FLTBLKG}$	FLT pin leakage current	FLT de-asserted High	-0.1	0.1	0.1	$\mu\text{A}$
<b>POWER GOOD INDICATION (PG)</b>						
$R_{PG}$	PG pin pull-down resistance	PG de-asserted Low	6.9			$\Omega$
$I_{PGKG}$	PG pin leakage current	PG asserted High	-1.5	1.5	1.5	$\mu\text{A}$

## 6.7 Timing Requirements

$-40^\circ\text{C} \leq T_J \leq +125^\circ\text{C}$ ,  $VIN = V_{DD} = 45\text{V}$  to  $60\text{V}$ ,  $OUT = \text{Open}$ ,  $R_{ILIM} = 931\Omega$ ,  $R_{IMON} = 2.55\text{k}\Omega$ ,  $V_{IREF} = 1\text{V}$ ,  $\overline{FLT} = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $PGOOD = 33\text{k}\Omega$  pull-up to  $3.3\text{V}$ ,  $C_{OUT} = 10\mu\text{F}$ ,  $C_{IN} = 10\text{nF}$ ,  $dVdT = \text{Open}$ ,  $ITIMER = \text{Open}$ ,  $V_{EN/UVLO} = 2\text{V}$ ,  $TEMP = \text{Open}$ ,  $MODE = \text{Open}$ . (All voltages referenced to GND, (unless otherwise noted))

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{OVP}$	Overvoltage protection response time	$V_{OVP} > V_{OVPR}$ V to SWEN $\downarrow$	1.5			$\mu\text{s}$
$t_{Insdly}$	Insertion delay	$V_{EN/UVLO} > V_{UVLO(R)}$ to SWEN $\uparrow$	16			ms
$t_{FFT}$	Fixed Fast-Trip response time Hard Short	$V_{DS} > V_{DSCOMP}$ to SWEN $\downarrow$	214			ns
$t_{SFT}$	Scalable Fast-Trip response time	$I_{OUT} > 3 \times I_{OCP}$ to $I_{OUT}\downarrow$	600			ns
$t_{ITIMER}$	Overcurrent blanking interval	$I_{OUT} = 1.5 \times I_{OCP}$ , $C_{ITIMER} = \text{Open}$	0			ms
$t_{ITIMER}$	Overcurrent blanking interval	$I_{OUT} = 1.5 \times I_{OCP}$ , $C_{ITIMER} = 4.7\text{nF}$	3			ms
$t_{RST}$	Auto-Retry Interval	Auto-retry variant, Primary mode (MODE = Open)	680			ms
$t_{REC}$	Fault Recovery Time	Secondary mode (MODE = GND), SWEN $\downarrow$ to SWEN $\uparrow$	8.9			$\mu\text{s}$
$t_{EN(DG)}$	EN/UVLO de-glitch time		12			$\mu\text{s}$
$t_{SWEN(TO)}$	SWEN low interval to disable fast recovery		35			$\mu\text{s}$
$t_{SU\_TMR}$	Start-up timeout interval	SWEN $\uparrow$ to $\overline{FLT}\downarrow$	6.6			s
$t_{Discharge}$	QOD discharge time (90% to 10% of $V_{OUT}$ )	$V_{SD} < V_{EN/UVLO} < V_{UVLO}$ , $C_{OUT} = 0.5\text{mF}$ , $V_{IN} = 51\text{V}$	872			ms
$t_{QOD}$	QOD enable timer	$V_{SD} < V_{EN/UVLO} < V_{UVLO}$	16			$\mu\text{s}$

## 6.8 Switching Characteristics

The output rising slew rate is internally controlled and constant across the entire operating voltage range so that the turn on timing is not affected by the load conditions. The rising slew rate can be adjusted by adding capacitance from the  $dVdt$  pin to ground. As  $C_{dVdt}$  is increased it will reduce the slew rate (SR). See Slew Rate and Inrush Current Control ( $dVdt$ ) section for more details. The Turn-Off Delay and Fall Time, however, are dependent on the RC time constant of the load capacitance ( $C_{OUT}$ ) and Load Resistance ( $R_L$ ). The Switching Characteristics are only valid for the power-up sequence where the supply is available in steady state condition and the load voltage is completely discharged before the device is enabled. Typical values are taken at  $T_J = 25^\circ\text{C}$  unless specifically noted otherwise.  $V_{IN} = 51\text{V}$ ,  $R_{OUT} = 2000\Omega$ ,  $C_{OUT} = 1\text{mF}$

PARAMETER		$C_{dVdt} = 22\text{ nF}$	$C_{dVdt} = \text{open}$	UNITS
$SR_{ON}$	Output rising slew rate	87	80	V/s
$t_{D,ON}$	Turn on delay	16.8	18	ms
$t_R$	Rise time	478	525.6	ms
$t_{ON}$	Turn on time	494.8	543.6	ms
$t_{D,OFF}$	Turn off delay (EN $\downarrow$ to SWEN $\downarrow$ )	1	1	$\mu\text{s}$
$t_F$	Fall time	Depends on $R_{OUT}$ and $C_{OUT}$		$\mu\text{s}$

## 6.9 Typical Characteristics

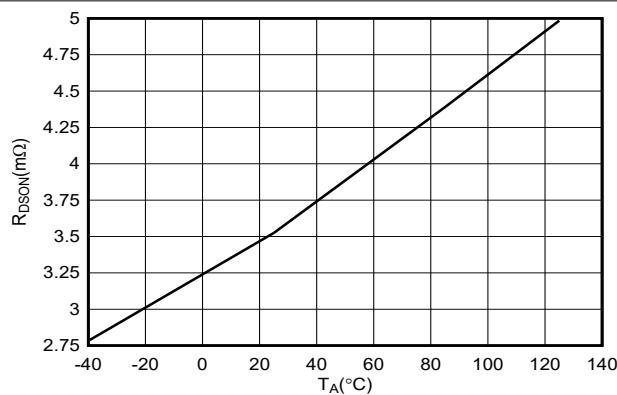


Figure 6-1. ON Resistance vs Temperature

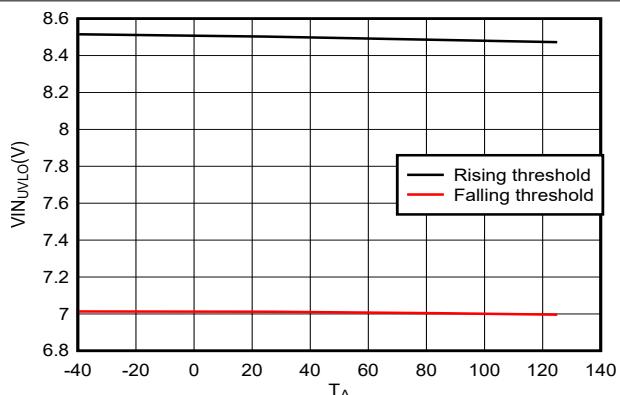


Figure 6-2. VIN Undervoltage Thresholds vs Temperature

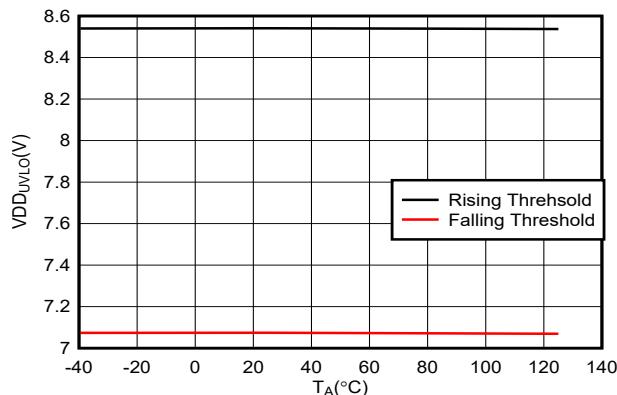


Figure 6-3. VDD Undervoltage Thresholds vs Temperature

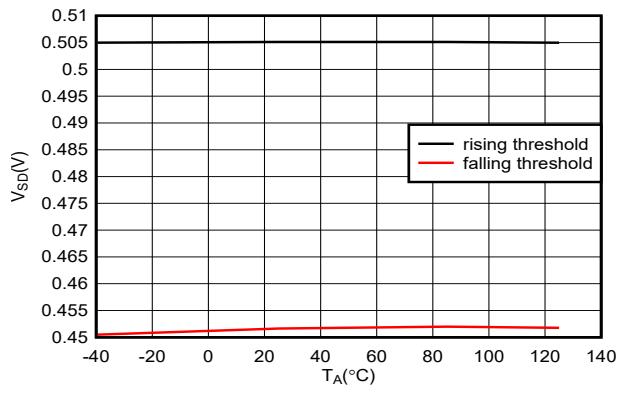


Figure 6-4. EN based Shutdown (VSD) Thresholds vs Temperature

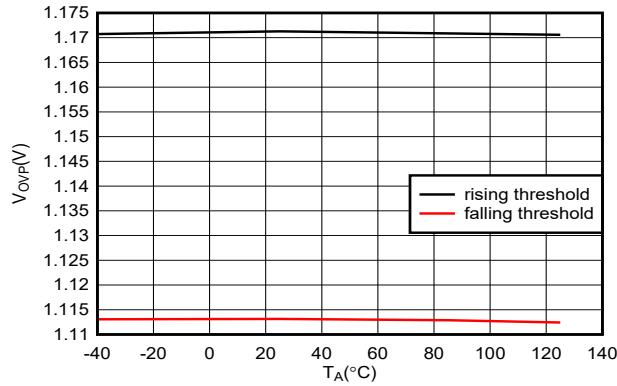


Figure 6-5. Overvoltage Pin(OVP) Thresholds vs Temperature

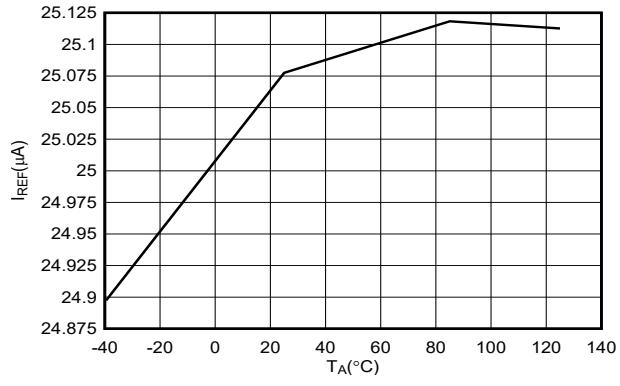


Figure 6-6. IREF Charging Current vs Temperature

## 6.9 Typical Characteristics (continued)

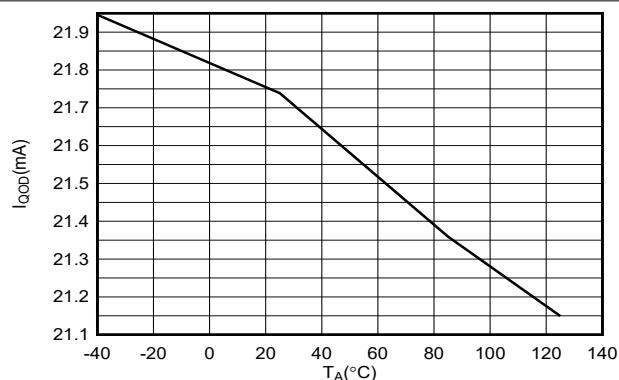


Figure 6-7. QOD Discharge Current vs Temperature

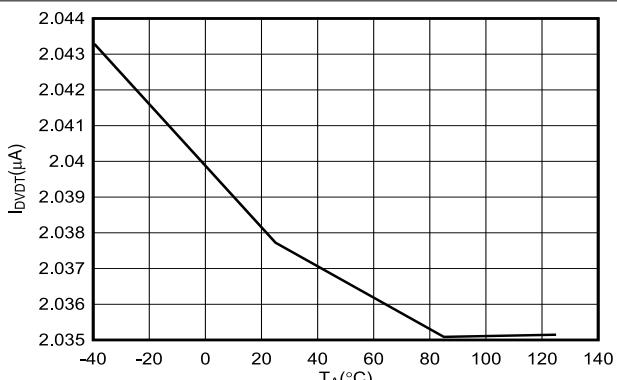


Figure 6-8. DVDT Current vs Temperature

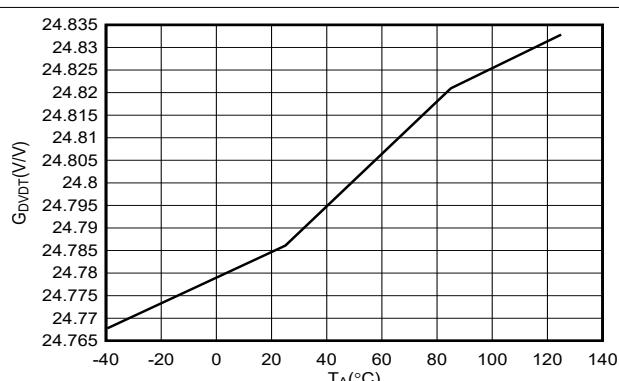


Figure 6-9. DVDT Gain vs Temperature

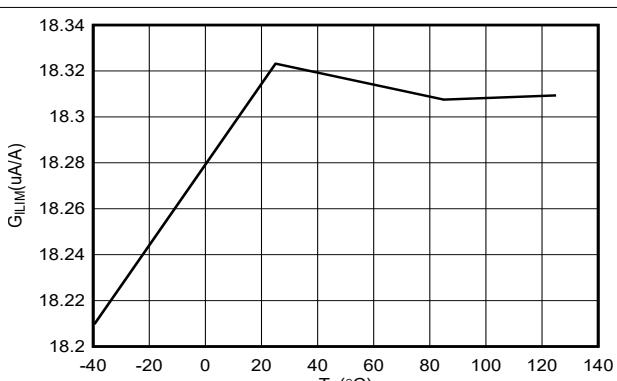


Figure 6-10. ILIM Gain vs Temperature

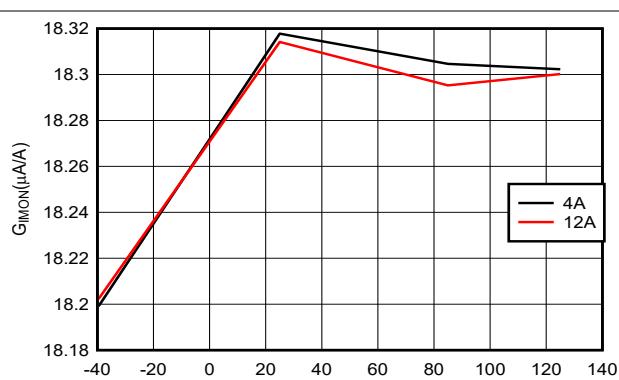


Figure 6-11. IMON Gain vs Temperature

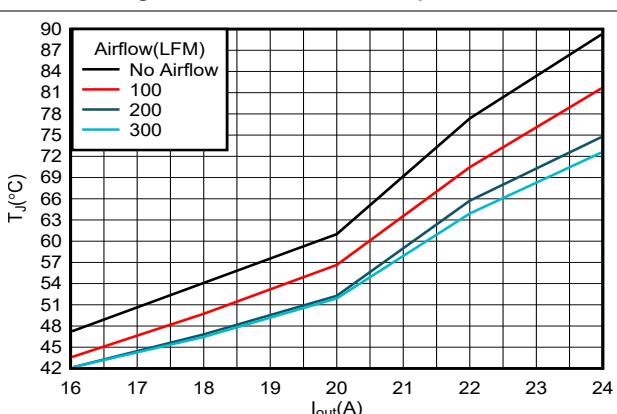


Figure 6-12. Junction Temperature vs Load Current ( $T_A = 25^\circ\text{C}$ , with and without Airflow)

## 6.9 Typical Characteristics (continued)

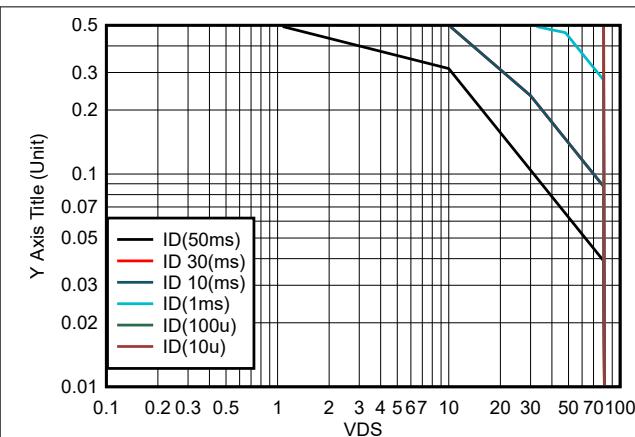


Figure 6-13. Allowed Operating Area (AOA) in Startup

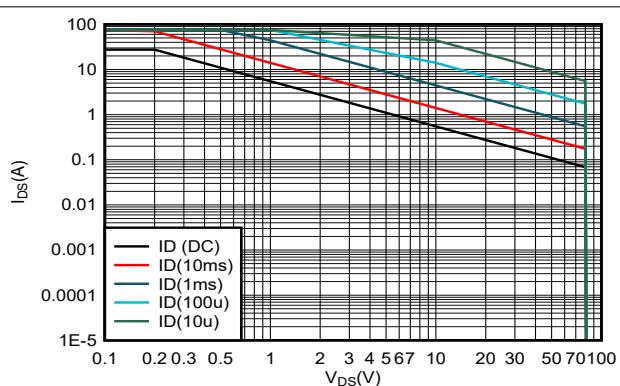
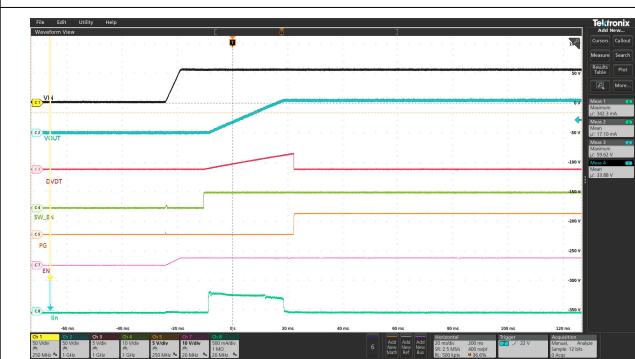
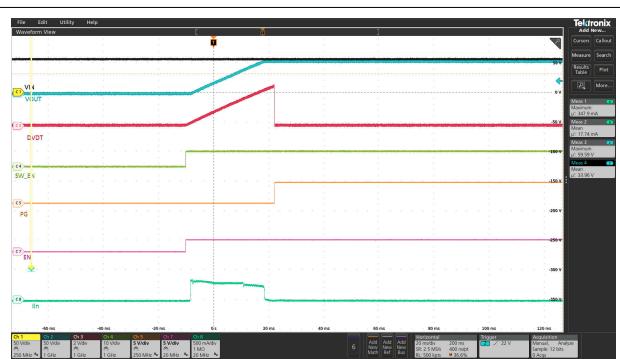


Figure 6-14. Allowed Operating Area (AOA) in Steady State



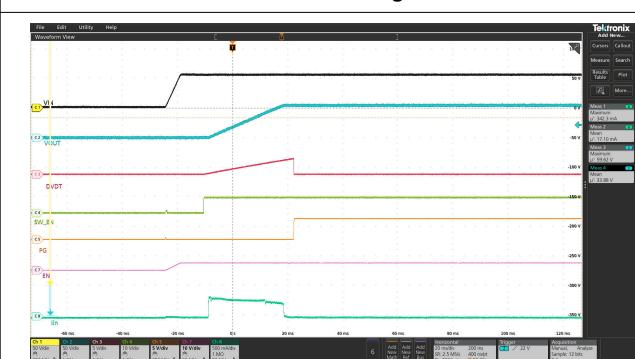
Input supply ramped up

Figure 6-15. Power Up Sequencing Using Input Supply with EN connected to VIN through Resistor



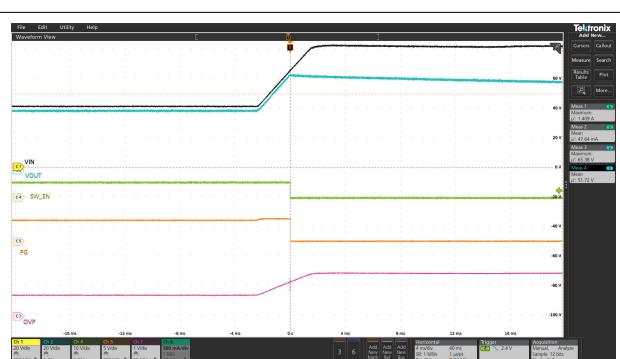
Input supply held steady, EN/UVLO pin toggled high

Figure 6-16. Power Up Using EN/UVLO Pin



$C_{OUT} = 144\mu F, C_{dVdt} = 22nF$

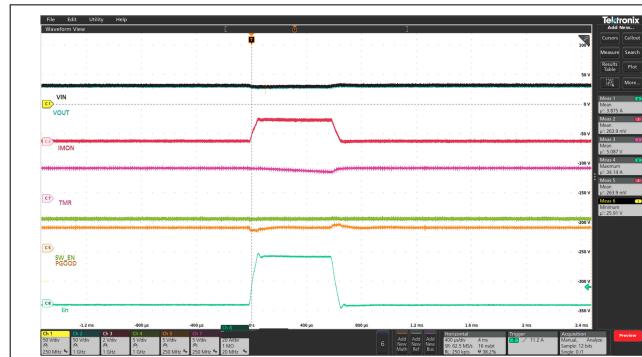
Figure 6-17. Inrush Current Control with Capacitive Load



Input supply ramped up above 65V

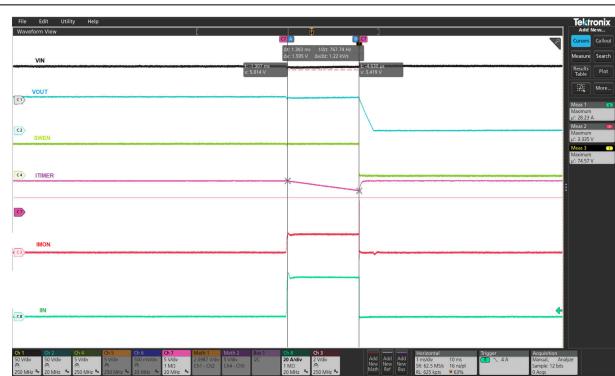
Figure 6-18. Input Overvoltage Protection Response with OVP threshold= 65V

## 6.9 Typical Characteristics (continued)



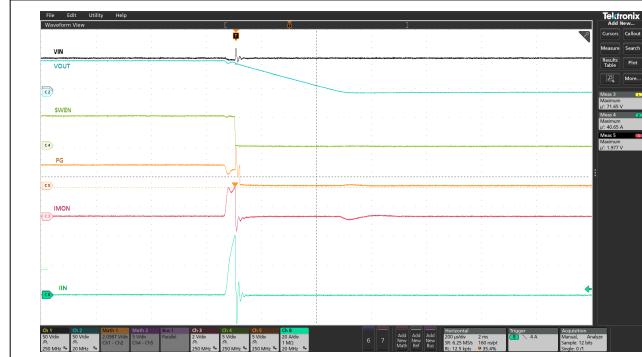
$I_{OCP} = 22A$ ,  $t_{TIMER} = 1.4ms$ ,  $I_{OUT}$  pulsed above the  $I_{OCP}$  threshold for short duration without triggering circuit-breaker response

**Figure 6-19. Peak Current Support Until Transient Overcurrent Blanking Timer expires**



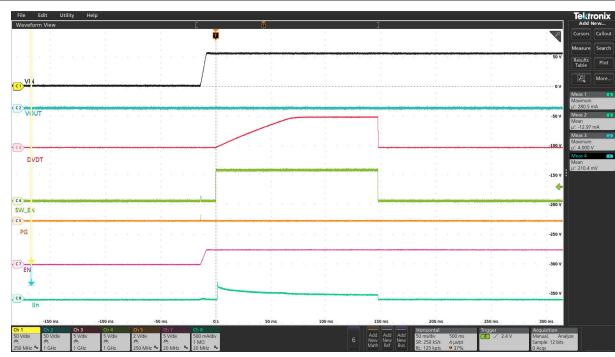
$I_{OCP} = 50A$ ,  $t_{TIMER} = 1.4ms$ ,  $I_{OUT}$  stays above the  $I_{OCP}$  threshold persistently to trigger circuit-breaker response

**Figure 6-20. Overcurrent Protection Response (Circuit-Breaker)**



$I_{OCP} = 22A$ , Output hard-short to GND while in steady.  $I_{OUT}$  rises above  $2 \times I_{OCP}$  triggers fast-trip response

**Figure 6-21. Short-Circuit Protection Response**



Device turned on using SWEN with output hard-short to GND. Device limits the current with foldback.

**Figure 6-22. Power Up into Short-Circuit**

## 7 Detailed Description

### 7.1 Overview

The TPS1685x is an eFuse with integrated power switch that is used to manage load voltage and load current. The device starts the operation by monitoring the VDD and IN bus. When  $V_{DD}$  and  $V_{IN}$  exceed the respective undervoltage protection (UVP) thresholds, the device waits for the insertion delay timer duration to allow the supply to stabilize before starting up. Next, the device samples the EN/UVLO pin. A high level on this pin enables the internal MOSFET to start conducting and allow current to flow from IN to OUT. When EN/UVLO is held low, the internal MOSFET is turned off.

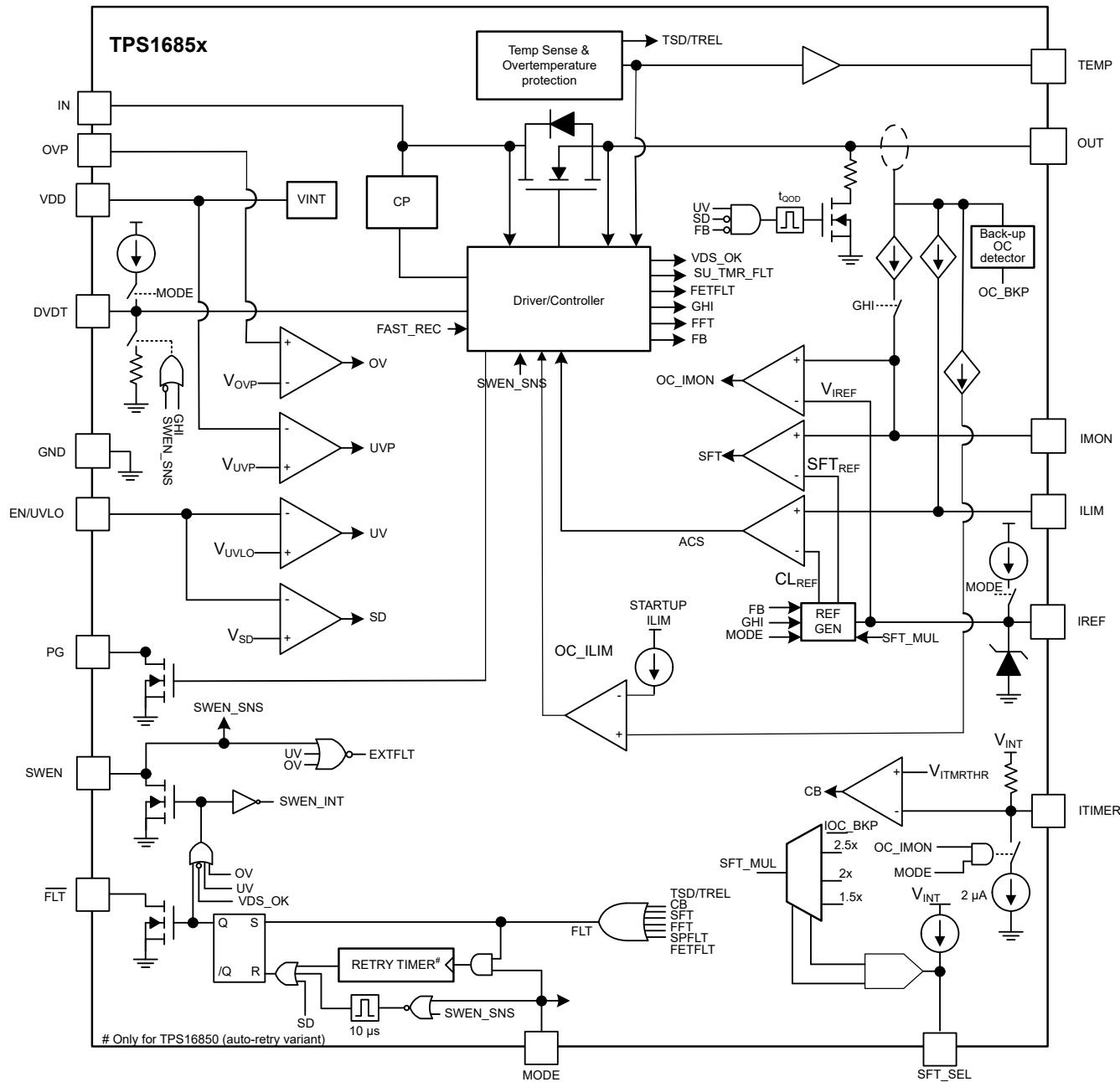
After a successful start-up sequence, the TPS1685x device now actively monitors the load current and input voltage, and controls the internal FET to verify that the user adjustable overcurrent protection threshold limit  $I_{LIM}$  is not exceeded and overvoltage spikes on IN pin are cut-off. This keeps the system safe from harmful levels of voltage and current. At the same time, a user adjustable overcurrent blanking timer allows the system to pass transient peaks in the load current profile without tripping the eFuse. Similarly, voltage transients on the supply line are intelligently masked to prevent nuisance trips. This provides a robust protection solution against real faults which is also immune to transients, thereby providing maximum system uptime.

The device has integrated high accuracy and high bandwidth analog load current monitor, which allows the system to precisely monitor the load current in steady state as well as during transients. This facilitates the implementation of advanced dynamic platform power management techniques to maximize system power utilization and throughput without sacrificing safety and reliability.

For systems needing higher load current support, multiple TPS1685x eFuses can be connected in parallel. All devices share current during start-up as well as steady state to avoid overstressing some of the devices more than others resulting in pre-mature or partial shutdown of the parallel chain. The devices synchronize the operating states to provide graceful startup, shutdown and response to faults.

The device has integrated protection circuits to help provide device safety and reliability under recommended operating conditions. The internal FET is protected at all time using the thermal shutdown mechanism, which turns off the FET whenever the junction temperature ( $T_j$ ) becomes too hot.

## 7.2 Functional Block Diagram

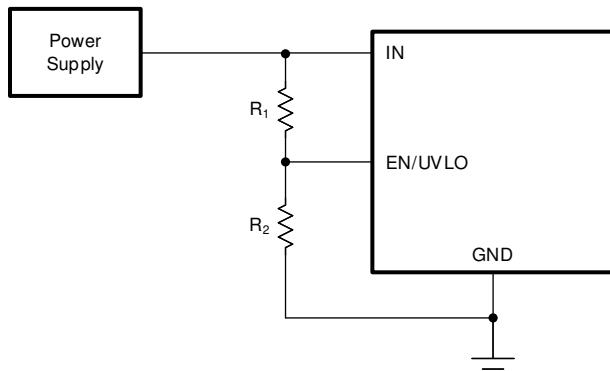


## 7.3 Feature Description

The TPS1685x eFuse is a compact, feature rich power management device that provides detection, protection and indication in the event of system faults.

### 7.3.1 Undervoltage Protection

The TPS1685x implements Undervoltage Lockout on VDD & VIN in case the applied voltage becomes too low for the system or device to properly operate. The Undervoltage lockout has a default lockout threshold of  $V_{UVP}$  internally on VDD and  $V_{UVPIN}$  on  $V_{IN}$ . Also, the UVLO comparator on the EN/UVLO pin allows the Undervoltage Protection threshold to be externally adjusted to a user defined value. The figure and equation below shows how a resistor divider can be used to set the UVLO set point for a given voltage supply.



**Figure 7-1. Adjustable Undervoltage Protection**

$$V_{IN(UV)} = V_{UVLO(R)} \frac{R_1 + R_2}{R_2} \quad (1)$$

The EN/UVLO pin implements a bi-level threshold.

1.  $V_{EN} > V_{UVLO(R)}$ : Device is fully ON.
2.  $V_{SD(F)} < V_{EN} < V_{UVLO(F)}$ : The FET along with most of the controller circuitry is turned OFF, except for some critical bias and digital circuitry. Holding the EN/UVLO pin in this state for  $> t_{QOD}$  activates the Output Discharge function.
3.  $V_{EN} < V_{SD(F)}$ : All active circuitry inside the part is turned OFF and the circuitry retains no digital state memory. The circuitry also resets any latched faults. In this condition, the device quiescent current consumption is minimal.

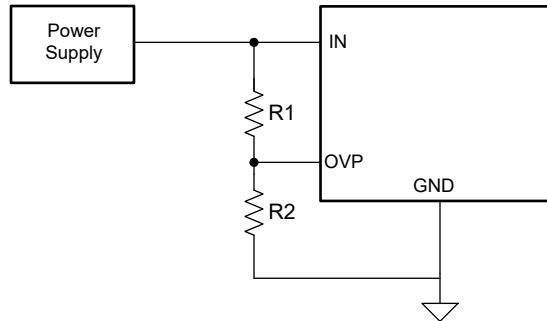
### 7.3.2 Insertion Delay

The TPS1685x implements insertion delay at start-up to verify the supply has stabilized before the device tries to turn on. This is to prevent any unexpected behavior in the system if the device tries to turn on while the card has not made firm contact with the backplane or if there is any supply ringing or oscillation during startup.

The device initially waits for the VDD supply to rise above the UVP threshold and all the internal bias voltages to settle. After that, the device remains off for an additional delay of  $T_{Insdly}$  irrespective of the EN/UVLO pin condition.

### 7.3.3 Overvoltage Protection

The TPS1685x implements overvoltage lockout to protect the load from input overvoltage conditions. A resistor divider needs to be connected on OVP pin to set the overvoltage set-point externally.

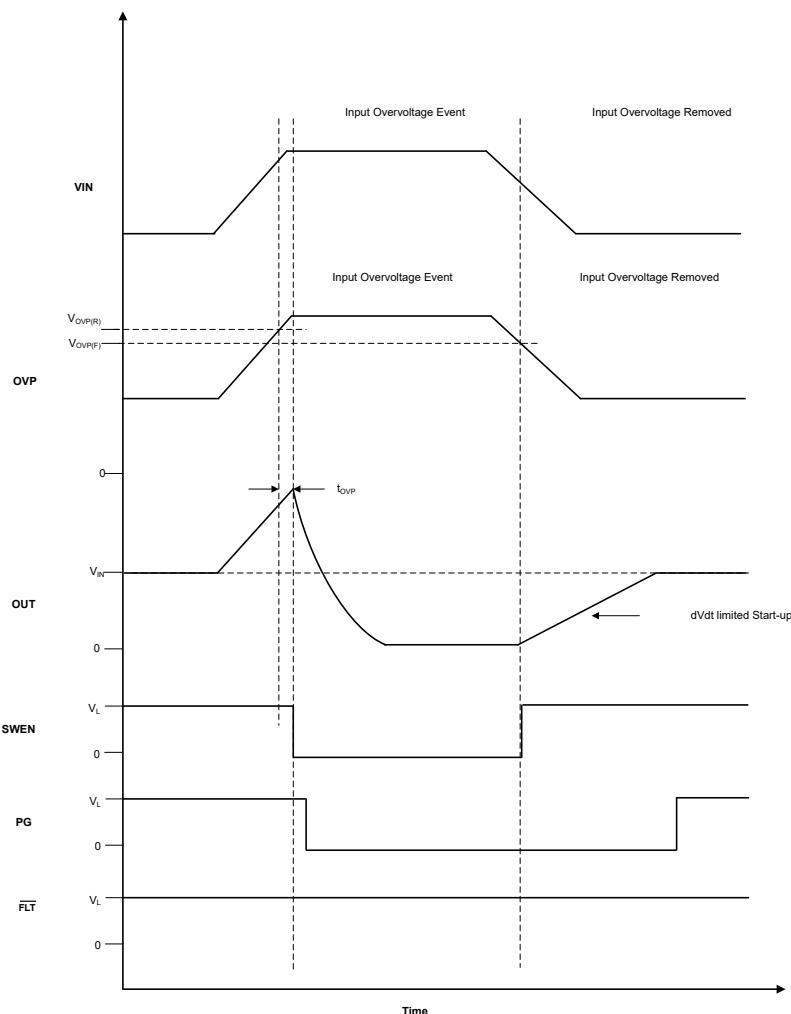


**Figure 7-2. Adjustable Overvoltage Protection**

$$V_{IN(OVP)} = V_{OVP(R)} \frac{R1 + R2}{R2} \quad (2)$$

When  $V_{IN}$  exceeds this value, the device turns off protecting the load from overvoltage.

The device also has a fixed internal OV protection on IN pin at  $V_{OVPR(IN)}$ .



**Figure 7-3. Input Overvoltage Protection Response**

### 7.3.4 Inrush Current, Overcurrent, and Short-Circuit Protection

TPS1685x incorporates four levels of protection against overcurrent:

1. Adjustable slew rate ( $dVdt$ ) for inrush current control
2. Fixed current limit ( $I_{start-up}$ ) for overcurrent protection during start-up
3. Circuit-breaker with an adjustable threshold ( $I_{OCP}$ ) and blanking timer ( $t_{ITIMER}$ ) for overcurrent protection during steady-state

#### 7.3.4.1 Slew rate ( $dVdt$ ) and Inrush Current Control

During hot plug events or while trying to charge a large output capacitance, there can be a large inrush current. If the inrush current is not managed properly, the inrush current can damage the input connectors and cause the system power supply to droop. This action can lead to unexpected restarts elsewhere in the system. The inrush current during turn-on is directly proportional to the load capacitance and rising slew rate. [Equation 3](#) can be used to find the slew rate (SR) required to limit the inrush current ( $I_{INRUSH}$ ) for a given load capacitance ( $C_{LOAD}$ ):

$$SR(V/ms) = \frac{I_{INRUSH}(A)}{C_{LOAD}(mF)} \quad (3)$$

A capacitor can be added to the DVDT pin to control the rising slew rate and lower the inrush current during turn-on. Slew rate control via DVDT pin holds true as long as the resulting startup current through the device is less than the  $I_{start-up}$  peak. The device limits the current at startup to not exceed  $I_{start-up}$  peak. The required  $CdVdt$  capacitance to produce a given slew rate can be calculated using [Equation 4](#).

$$C_{DVDT}(nF) = \frac{48}{SR(V/ms)} \quad (4)$$

The fastest output slew rate is achieved by leaving the dVdt pin open.

#### Note

1. TI recommends using a minimum dvdt capacitor of 22nF.
2. High input slew rates in combination with high input power path inductance can result in oscillations during start-up. This can be mitigated using one or more of the following steps:
  - a. Reduce the input inductance.
  - b. Increase the capacitance on VIN pin.
  - c. Increase the dVdt pin capacitance to reduce the slew rate or increase the start-up time.

#### 7.3.4.1.1 Start-Up Time Out

If the start-up is not completed, that is, the FET is not fully turned on within a certain timeout interval ( $t_{SU\_TMR}$ ) after SWEN is asserted, the device registers a fault. FLT is asserted low and the device goes into latch-off or auto-retry mode depending on the device configuration.

#### 7.3.4.2 Steady-State Overcurrent Protection (Circuit-Breaker)

The TPS1685x responds to output overcurrent conditions during steady-state by performing a circuit-breaker action after a user-adjustable transient fault blanking interval. This action allows the device to support a higher peak current for a short user-defined interval but also provides robust protection in case of persistent output faults.

The device constantly senses the output load current and provides an analog current output ( $I_{IMON}$ ) on the IMON pin which is proportional to the load current, which in turn produces a proportional voltage ( $V_{IMON}$ ) across the IMON pin resistor ( $R_{IMON}$ ) as per [Equation 5](#).

$$V_{IMON} = I_{OUT} \times G_{IMON} \times R_{IMON} \quad (5)$$

Where  $G_{IMON}$  is the current monitor gain ( $I_{IMON} : I_{OUT}$ )

The overcurrent condition is detected by comparing this voltage against the voltage on the IREF pin as a reference. The reference voltage ( $V_{IREF}$ ) can be controlled in two ways, which sets the overcurrent protection threshold ( $I_{OCP}$ ) accordingly.

- In the standalone or primary mode of operation, the internal current source interacts with the external IREF pin resistor ( $R_{IREF}$ ) to generate the reference voltage. Driving the IREF pin from an external low impedance reference voltage source is also possible, as shown in [Equation 6](#).

$$V_{IREF} = I_{IREF} \times R_{IREF} \quad (6)$$

- In a primary and secondary parallel configuration, the primary eFuse or controller drives the voltage on the IREF pin to provide an external reference ( $V_{IREF}$ ) for all the secondary devices in the chain.

The overcurrent protection threshold during steady-state ( $I_{OCP}$ ) can be calculated using [Equation 7](#).

$$I_{OCP} = \frac{V_{IREF}}{G_{IMON} \times R_{IMON}} \quad (7)$$

After an overcurrent condition is detected, that is the load current exceeds the user adjustable over current limit threshold ( $I_{OCP}$ ), but stays lower than the short-circuit threshold ( $I_{SFT}$ ), the device starts discharging the ITIMER pin capacitor using an internal pulldown current. If the load current drops below the current limit threshold before the ITIMER capacitor discharges by  $\Delta V_{ITIMER}$ , the ITIMER is reset by pulling up to  $V_{INT}$  internally and the circuit-breaker action is not engaged. This action allows short overload transient pulses to pass through the device without tripping the circuit. If the overcurrent condition persists, the ITIMER capacitor continues to discharge and after the change falls by  $\Delta V_{ITIMER}$ , the circuit-breaker action turns off the FET immediately. At the same time, the ITIMER cap is charged up to  $V_{INT}$  again to the default state before the next overcurrent event. This action verifies that the full blanking timer interval is provided for every overcurrent event. [Equation 8](#) can be used to calculate the  $R_{IMON}$  value for the desired overcurrent threshold.

$$R_{IMON} = \frac{V_{IREF}}{G_{IMON} \times I_{OCP}} \quad (8)$$

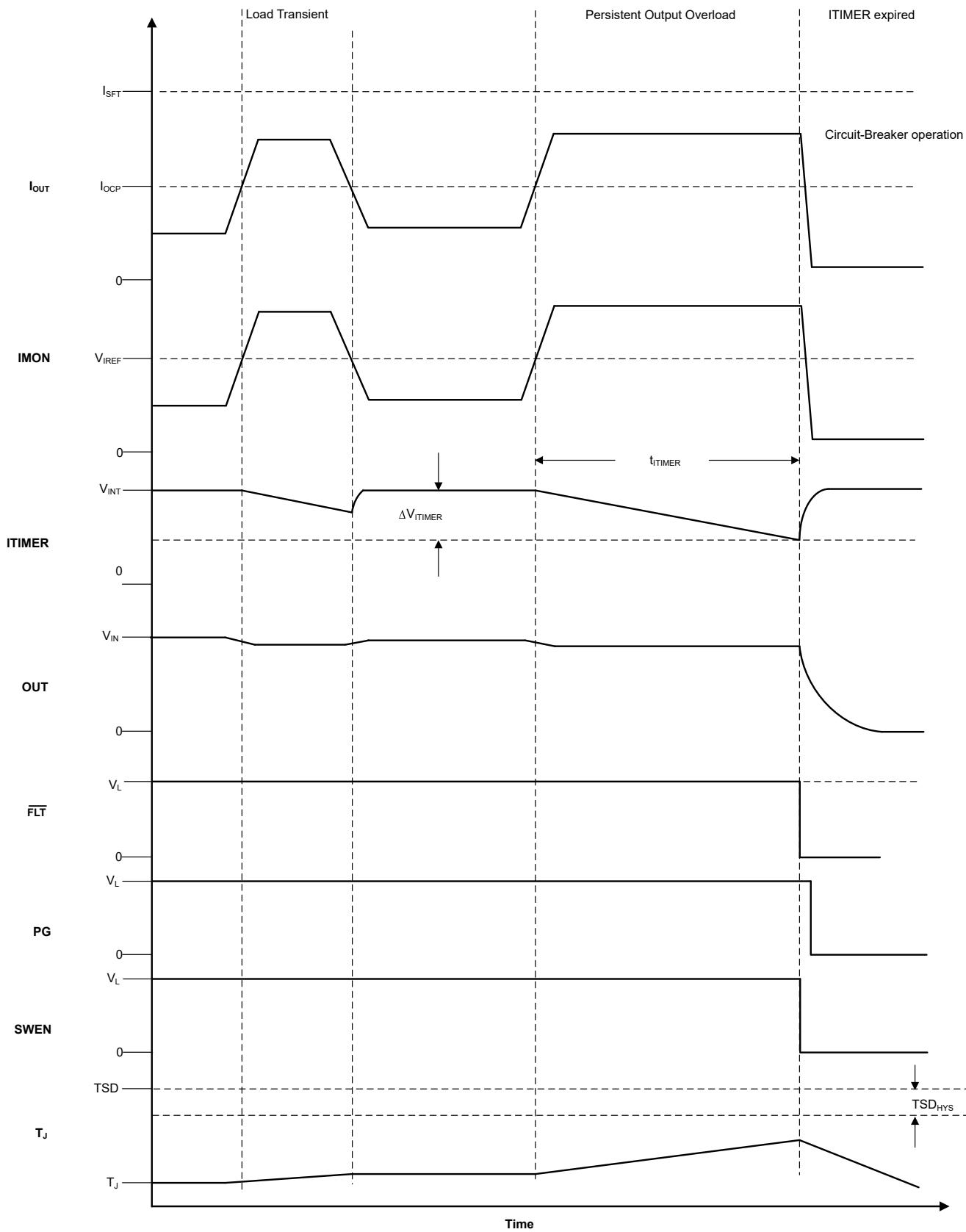
The duration for which transients are allowed can be adjusted using an appropriate capacitor value from ITIMER pin to ground. The transient overcurrent blanking interval can be calculated using [Equation 9](#).

$$t_{ITIMER}(ms) = \frac{C_{ITIMER}(nF) \times \Delta V_{ITIMER}(V)}{I_{ITIMER}(\mu A)} \quad (9)$$

#### Note

1. Leave the ITIMER pin open to allow the part to break the circuit with the minimum possible delay. However, this makes the circuit-breaker response extremely sensitive to noise and can cause false tripping during load transients.
2. Shorting the ITIMER pin to ground results in minimum overcurrent response delay (similar to ITIMER pin open condition), but increases the quiescent current – not a recommended mode of operation.
3. Increasing the ITIMER cap value extends the overcurrent blanking interval. However, the time needed is also extended for the ITIMER capacitor to recharge up to  $V_{INT}$  before the next overcurrent event. If the next overcurrent event occurs before the ITIMER cap is recharged fully, discharging to the VITIMER threshold takes less time, thereby providing a shorter blanking interval than intended.

**Figure 7-4** illustrates the overcurrent response for TPS1685x eFuse. After the part shuts down due to a circuit-breaker fault, the parts either stays latched off (TPS16851 variant) or restarts automatically after a fixed delay (TPS16850 variant).



**Figure 7-4. Steady-State Overcurrent (Circuit-Breaker) Response**

### 7.3.4.3 Active Current Limiting During Start-Up

The TPS1685x responds to output overcurrent conditions during start-up by actively limiting the current. The startup current limit is internally fixed to  $I_{\text{start-up}}$ .

When the load current during start-up exceeds  $I_{\text{start-up}}$ , the device tries to regulate and hold the load current at  $I_{\text{start-up}}$ .

During current regulation, the output voltage drops, resulting in increased device power dissipation across the FET. If the device internal temperature ( $T_J$ ) exceeds the thermal shutdown threshold (TSD), the FET is turned off. After the part shuts down due to a TSD fault, the device either stays latched off (TPS16851 variants) or restarts automatically after a fixed delay (TPS16850 variants). See [Overtemperature protection](#) section for more details on device response to overtemperature.

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#### Note

The active current limit block employs a foldback mechanism during start-up based on the output voltage ( $V_{\text{OUT}}$ ). When  $V_{\text{OUT}}$  is below the foldback threshold ( $V_{\text{FB}}$ ), the current limit threshold is further lowered.

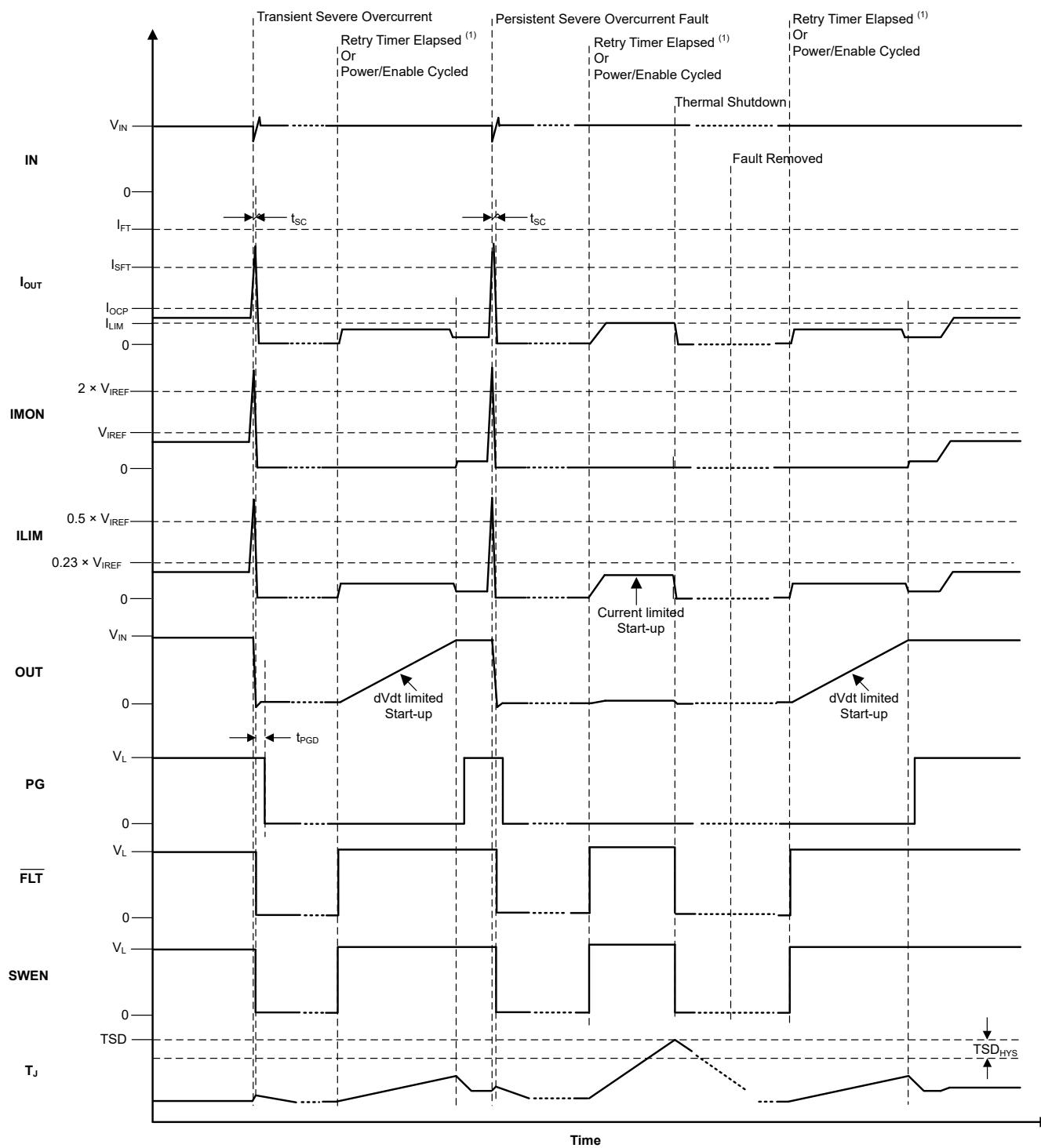
### 7.3.4.4 Short-Circuit Protection

During a output short-circuit event, the current through the device increases very rapidly. When an output short-circuit is detected, the internal fast-trip comparator triggers a fast protection sequence to prevent the current from building up further and causing any damage or excessive input supply droop. The fast-trip comparator employs a scalable threshold ( $I_{\text{SFT}}$ ) during steady-state.  $I_{\text{SFT}}$  can be selected by resistor on SFT\_SEL pin. This enables the user to adjust the fast-trip threshold as per system rating, rather than using a high fixed threshold which is not always suitable for all systems. After the current exceeds the fast-trip threshold, the TPS1685x turns off the FET within  $t_{\text{SFT}}$ . The device also employs a higher fixed fast-trip threshold ( $I_{\text{FFT}}$ ) to provide fast protection against hard short-circuits during steady-state (FET in linear region). After the current exceeds  $I_{\text{FFT}}$ , the FET is turned off completely within  $t_{\text{FFT}}$ .

**Table 7-1. Device Functional Modes Based on Resistor on SFT\_SEL Pin**

$I_{\text{SFT\_SEL}}$	SFT_SEL pin	MODE pin
$I_{\text{OC\_BKP}}$	$R_{\text{SFT\_SEL}} < 95\text{k}\Omega$	Open
$2.5 \times I_{\text{OCP}}$	$105\text{k}\Omega < R_{\text{SFT\_SEL}} < 195\text{k}\Omega$	Open
$2.8 \times I_{\text{OCP}}$	$105\text{k}\Omega < R_{\text{SFT\_SEL}} < 195\text{k}\Omega$	Gnd
$2 \times I_{\text{OCP}}$	$205\text{k}\Omega < R_{\text{SFT\_SEL}} < 295\text{k}\Omega$	Open
$2.26 \times I_{\text{OCP}}$	$205\text{k}\Omega < R_{\text{SFT\_SEL}} < 295\text{k}\Omega$	Gnd
$1.5 \times I_{\text{OCP}}$	$305\text{k}\Omega < R_{\text{SFT\_SEL}}$	Open
$1.71 \times I_{\text{OCP}}$	$305\text{k}\Omega < R_{\text{SFT\_SEL}}$	Gnd

Figure 7-5 illustrates the short-circuit response for TPS1685x eFuse.



**Figure 7-5. Short-Circuit Response**

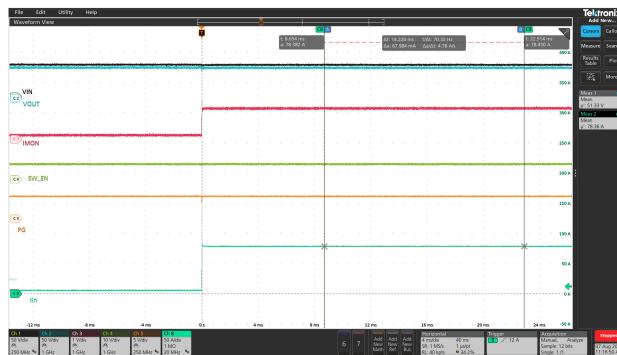
### 7.3.5 Analog Load Current Monitor (IMON)

The TPS1685x allows the system to monitor the output load current accurately by providing an analog current on the IMON pin which is proportional to the current through the FET. The benefit of having a current output is that the signal can be routed across a board without adding significant errors due to voltage drop or noise coupling from adjacent traces. The current output also allows the IMON pins of multiple TPS1685x devices to be

tied together to get the total current in a parallel configuration. The IMON signal can be converted to a voltage by dropping it across a resistor at the point of monitoring. The user can sense the voltage ( $V_{IMON}$ ) across the  $R_{IMON}$  to get a measure of the output load current using [Equation 10](#).

$$I_{OUT} = \frac{V_{IMON}}{G_{IMON} \times R_{IMON}} \quad (10)$$

The TPS1685x IMON circuit is designed to provide high bandwidth and high accuracy across load and temperature conditions, irrespective of board layout and other system operating conditions. This design allows the IMON signal to be used for advanced dynamic platform power management techniques such as Intel® PSYS or PROCHOT# to maximize system power usage and platform throughput without sacrificing safety or reliability.



**Figure 7-6. Analog Load Current Monitor Response**

#### Note

1. The IMON pin provides load current monitoring information only during steady-state. During inrush, the IMON pin reports zero load current.
2. The ILIM pin reports the individual device load current at all times and can also be used as an analog load current monitor for each individual device.
3. Care must be taken to minimize parasitic capacitance on the IMON and ILIM pins to avoid any impact on the overcurrent and short-circuit protection timing.

#### 7.3.6 Mode Selection (MODE)

This pin can be used to configure the TPS1685x as a primary device in a chain along with other TPS1685x eFuses, designated as secondary devices. This feature allows some of the TPS1685x pin functions to be changed to aid the primary and secondary parallel connection.

This pin is sampled at power up. Leaving the pin open configures the pin as a primary or standalone device. Connecting this pin to GND configures the pin as a secondary device.

The following functions are disabled in secondary mode and the device relies on the primary device to provide this functionality:

1. IREF internal current source
2. DVDT internal current source
3. Overcurrent detection in steady-state for circuit-breaker response
4. PG de-assertion (pulldown) after reaching steady-state
5. Latch-off after fault

In secondary mode, the following functions are still active:

1. Overtemperature protection
2. Start-up current limit
3. Active current sharing during inrush as well as steady-state

4. Analog current monitor (IMON) in steady state
5. Steady-state overcurrent detection based on IMON. This is indicated by pulling ITIMER pin low internally, but does not trigger circuit-breaker action on ITIMER expiry. Rather, the pin relies on the primary device to start a dedicated ITIMER and then trigger the circuit-breaker action for the whole chain by pulling SWEN low after the ITIMER expiry. However, the secondary devices use an internal overcurrent timer as a backup in case the primary device fails to initiate circuit-breaker action for an extended period of time. Refer to [Single Point Failure Mitigation](#) section for details.
6. Each device still has individual scalable and fixed fast-trip thresholds to protect itself. The individual short-circuit protection threshold is set to higher values in secondary mode so that the primary device can lower it further for the whole system.
7. Individual OVP is set to maximum in secondary device so that the primary can lower individual OVP further for the whole system.
8. FLT assertion based on individual device fault detection (except circuit-breaker).
9. PG de-assertion control during inrush and assertion control after device reaches steady state. However, after that in steady state, the secondary device no longer controls the de-assertion of the PG in case of faults.
10. SWEN assertion or de-assertion based on internal events as well as FET ON and OFF control based on SWEN pin status.

In secondary mode, the device behavior during short-circuit and fast-trip is also altered. More details are available in the [Short-Circuit Protection](#) section.

### 7.3.7 Parallel Device Synchronization (SWEN)

The SWEN pin is a signal which is driven high when the FET must be turned ON. When the SWEN pin is driven low (internally or externally), the pin signals the driver circuit to turn OFF the FET. This pin serves both as a control and handshake signal and allows multiple devices in a parallel configuration to synchronize the FET ON and OFF transitions.

**Table 7-2. SWEN Summary**

Device State	FET Driver Status	SWEN
Steady-state	ON	H
Inrush	ON	H
Overtemperature shutdown	OFF	L
Auto-retry timer running	OFF	L
Undervoltage (EN/UVLO)	OFF	L
Undervoltage (VDD UVP)	OFF	L
Undervoltage (VIN UVP)	OFF	L
Insertion delay	OFF	L
Overvoltage lockout (VIN OVP)	OFF	L
Transient overcurrent	ON	H
Circuit-breaker (persistent overcurrent followed by ITIMER expiry)	OFF	L
Fast-trip	OFF	L
Fault response mono-shot running (MODE = GND)	OFF	L
Fault response mono-shot expired (MODE = GND)	ON	H
IMON pin open (steady-state)	OFF	L
IMON pin short (steady-state)	OFF	L
FET health fault	OFF	L

**Note**

1. The SWEN is an open-drain pin but has a weak internal pullup to  $V_{INT}$ .
2. The SWEN can also be pulled up to an external supply. TI recommends to use a system standby rail which is derived from the input of the eFuse.

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In a primary and secondary parallel configuration, the SWEN pin is used by the primary device to control the on and off transitions of the secondary devices. At the same time, the pin allows the secondary devices to communicate any faults or other condition which can prevent the pin from turning on to the primary device. Refer to [Fault Response and Indication \(FLT\)](#) for more details.

To maintain state machine synchronization, the devices rely on SWEN level transitions as well as timing for handshakes. This verifies that all the devices turn ON and OFF synchronously and in the same manner (for example, DVDT controlled or current limited start-up). There are also fail-safe mechanisms in the SWEN control and handshake logic to verify that the entire chain is turned off safely even if the primary device is unable to take control in case of a fault.

**Note**

TI recommends to keep the parasitic loading on the SWEN pin to a minimum to avoid synchronization timing issues.

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### 7.3.8 Stacking Multiple eFuses for Unlimited Scalability

For systems needing higher current than supported by a single TPS1685x, multiple TPS1685x or TPS1689x devices can be connected in parallel to deliver the total system current. Conventional eFuses can not share current equally between themselves during steady-state due to mismatches in the path resistances (which includes the individual device  $R_{DS(on)}$  variation from part to part, as well as the parasitic PCB trace resistance). This fact can lead to multiple problems in the system:

1. Some devices always carry higher current as compared to other devices, which can result in accelerated failures in those devices and an overall reduction in system operational lifetime.
2. As a result, thermal hotspots form on the board, devices, traces, and vias carrying higher current, leading to reliability concerns for the PCB. In addition, this problem makes thermal modeling and board thermal management more challenging for designers.
3. The devices carrying higher current can hit the individual circuit-breaker threshold prematurely even while the total system load current is lower than the overall circuit-breaker threshold. This action can lead to false tripping of the eFuse during normal operation. This has the effect of lowering the current-carrying capability of the parallel chain. In other words, the current rating of the parallel eFuse chain must be de-rated as compared to the sum of the current ratings of the individual eFuses. This de-rating factor is a function of the path resistance mismatch, the number of devices in parallel, and the individual eFuse circuit-breaker accuracy.

The need for de-rating has an adverse impact on the system design. The designer is forced to make one of these trade-offs:

1. Limit the operating load current of the system to below the derated current threshold of the eFuse chain. This tradeoff means lower platform capabilities than are supported by the power supply (PSU).
2. Increase the overall circuit-breaker threshold to allow the desired system load current to pass through without tripping. As a consequence, the power supply (PSU) must be oversized to deliver higher currents during faults to account for the de-grading of the overall circuit-breaker accuracy.

In either case, the system suffers from poor power supply utilization, which can mean sub-optimal system throughput or increased installation and operating costs, or both.

The TPS1685x uses a proprietary technique to address these problems and provide unlimited scalability of the solution by paralleling as many eFuses as needed. This is incorporated without unequal current sharing or any degradation in accuracy.

For this scheme to work correctly, the devices must be connected in the following manner:

- The SWEN pins of all the devices are connected together.
- The IMON pins of all the devices must be connected together. The  $R_{IMON}$  resistor value on the combined IMON pin can be calculated using [Equation 11](#).

$$R_{IMON} = \frac{V_{IREF}}{G_{IMON} \times I_{OCP(TOTAL)}} \quad (11)$$

- The  $R_{ILIM}$  for each individual eFuse must be selected based on [Equation 12](#).

$$R_{ILIM} = \frac{1.1 \times N \times R_{IMON}}{3} \quad (12)$$

Where N = number of devices in parallel chain.

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#### Note

The active current sharing scheme is engaged when the current through any eFuse while in steady-state exceeds the individual current sharing threshold set by the  $R_{ILIM}$  based on [Equation 13](#).

$$R_{ILIM} = \frac{1.1 \times V_{IREF}}{3 \times G_{ILIM} \times I_{LIM(ACS)}} \quad (13)$$

The active current sharing scheme is disengaged when the total system current exceeds the system overcurrent (circuit-breaker) threshold ( $I_{OCP(TOTAL)}$ ).

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#### 7.3.8.1 Current Balancing During Start-Up

The TPS1685x implements a proprietary current balancing mechanism during start-up, which allows multiple TPS1685x devices connected in parallel to share the inrush current and distribute the thermal stress across all the devices. This feature helps to complete a successful start-up with all the devices and avoid a scenario where some of the eFuses hit thermal shutdown prematurely. This in effect increases the inrush current capability of the parallel chain. The improved inrush performance makes supporting very large load capacitors possible on high current platforms without compromising the inrush time or system reliability.

#### 7.3.9 Analog Junction Temperature Monitor (TEMP)

The device allows the system to monitor the junction temperature ( $T_J$ ) accurately by providing an analog voltage on the TEMP pin which is proportional to the temperature of the die. This voltage can be connected to the ADC input of a host controller or eFuse with digital telemetry. In a multi-device parallel configuration, the TEMP outputs of all devices can be tied together. In this configuration, the TEMP signal reports the temperature of the hottest device in the chain.

#### 7.3.10 Overtemperature Protection

The TPS1685x employs an internal thermal shutdown mechanism to protect itself when the internal FET becomes too hot to operate safely. When the TPS16851 detects thermal overload, the device shuts down and remains latched-off until the device is power cycled or re-enabled. When the TPS16850 detects thermal overload, the device remains off until the device has cooled down sufficiently. Thereafter, the device remains off for an additional delay of  $t_{RST}$  after which the device automatically retries to turn on if the device is still enabled.

**Table 7-3. Overtemperature Protection Summary**

DEVICE	ENTER TSD	EXIT TSD
TPS16851 (Latch-Off)	$T_J \geq TSD$	$T_J < TSD - TSD_{HYS}$ VDD cycled to 0V and then above $V_{UVP(R)}$ or EN/UVLO toggled below $V_{SD(F)}$
TPS16850 (Auto-Retry)	$T_J \geq TSD$	$T_J < TSD - TSD_{HYS}$ $t_{RST}$ timer expired or VDD cycled to 0V and then above $V_{UVP(R)}$ or EN/UVLO toggled below $V_{SD(F)}$

### 7.3.11 Fault Response and Indication ( $\overline{FLT}$ )

Table 7-4 summarizes the device response to various fault conditions.

**Table 7-4. Fault Summary**

Event or Condition	Device Response	Fault Latched Internally	FLT Pin Status	Delay
Steady-state	None	N/A	H	
Inrush	None	N/A	H	
Overtemperature	Shutdown	Y	L	
Undervoltage (EN/UVLO)	Shutdown	N	H	
Undervoltage (VDD UVP)	Shutdown	N	H	
Undervoltage (VIN UVP)	Shutdown	N	H	
Overvoltage (VIN OVP)	Shutdown	N	H	
Transient overcurrent	None	N	H	
Persistent overcurrent (steady-state)	Circuit-Breaker	Y	L	$t_{ITIMER}$
Persistent overcurrent (start-up)	Current Limit	N	L	
Short-circuit (primary mode)	Fast-trip	Y	L	$t_{FT}$
Short-circuit (secondary mode)	Fast-trip followed by current limited Start-up	N	H	
ILIM pin open (steady-state)	Active current sharing loop always active	N	H	
ILIM pin short (steady-state)	Active current sharing loop disabled	N	H	
IMON pin open (steady-state)	Shutdown	Y	L	
IMON pin short (steady-state)	Shutdown (If $I_{OUT} > I_{OC\_BKP}$ )	Y	L	50 $\mu$ s
IREF pin open (steady-state)	Shutdown (if $I_{OUT} > I_{OC\_BKP}$ )	Y	L	$t_{ITIMER}$
IREF pin short (steady-state)	Shutdown	Y	L	
ITIMER pin forced to high voltage	Shutdown (if $I_{OUT} > I_{OCP}$ or $I_{OUT} > I_{OC\_BKP}$ )	Y	L	$t_{SPFAIL\_TMR}$
Start-up timeout	Shutdown	Y	L	$t_{SU\_TMR}$
FET health fault (G-S)	Shutdown	Y	L	10 $\mu$ s
FET health fault (G-D)	Shutdown	Y	L	
FET health fault (D-S)	Shutdown	N	L	$t_{SU\_TMR}$
External fault (SWEN pulled low externally while device is not in UV or OV)	Shutdown	Y	L	

$\overline{FLT}$  is an open-drain pin and must be pulled up to an external supply.

The device response after a fault varies based on the mode of operation:

1. During standalone or primary mode of operation (MODE = OPEN), the device latches a fault and follows the auto-retry or latch-off response as per the device selection. When the device turns on again, the device follows the typical DVDT limited start-up sequence.
2. During the secondary mode of operation (MODE = GND), if the device detects any fault, the device pulls the SWEN pin low momentarily to signal the event to the primary device and thereafter relies on the primary to take control of the fault response. However, if the primary device fails to register the fault, there is a failsafe mechanism in the secondary device to turn off the entire chain and enter a latch-off condition. Thereafter, the device can be turned on again only by power cycling VDD below  $V_{UVF}$  or by cycling EN/UVLO pin below  $V_{SD(F)}$ .

For faults that are latched internally, power cycling the part or pulling the EN/UVLO pin voltage below  $V_{SD(F)}$  clears the fault and the pin is de-asserted. This action also clears the  $t_{RST}$  timer (auto-retry variants only). Pulling the EN/UVLO just below the UVLO threshold has no impact on the device in this condition. This is true for both latch-off and auto-retry variants.

### 7.3.12 Power Good Indication (PG)

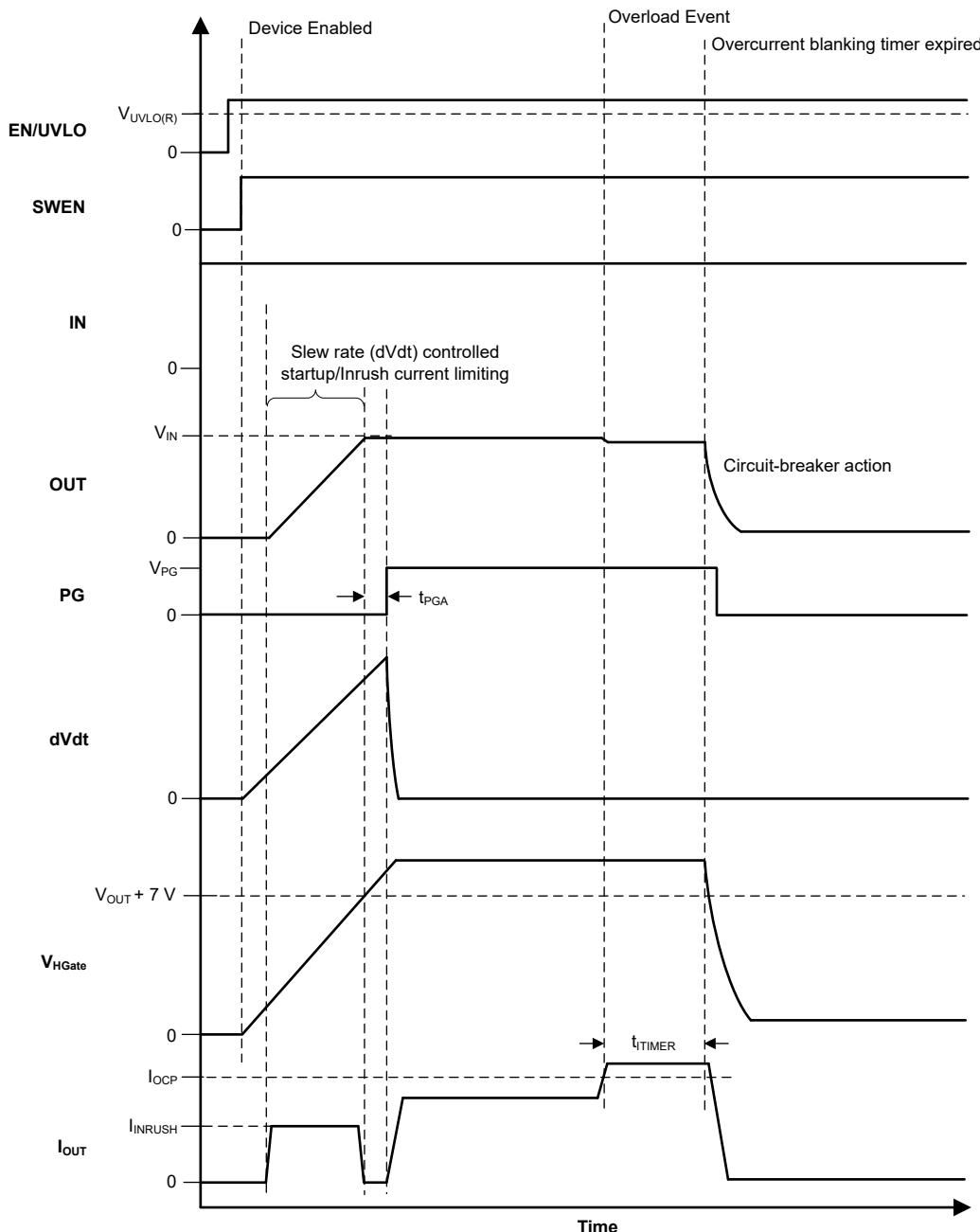
Power Good indication is an active high output which is asserted high to indicate when the device is in steady-state and capable of delivering maximum power.

**Table 7-5. PG Indication Summary**

Event or Condition	FET Status	PG Pin Status	PG Delay
Undervoltage ( $V_{EN} < V_{UVLO}$ )	OFF	L	$t_{PGD}$
$V_{IN} < V_{UVP}$	OFF	L	
$V_{DD} < V_{UVP}$	OFF	L	
Oversupply ( $V_{IN} > V_{OVP}$ )	OFF	L	$t_{PGD}$
Steady-state	ON	H	$t_{PGA}$
Inrush	ON	L	$t_{PGA}$
Transient overcurrent	ON	H	N/A
Circuit-breaker (persistent overcurrent followed by ITIMER expiry)	OFF	L (MODE = H) H (MODE = L)	$t_{PGD}$ N/A
Fast-trip	OFF	L (MODE = H) H (MODE = L)	$t_{PGD}$ N/A
Overtemperature	Shutdown	L (MODE = H) H (MODE = L)	$t_{PGD}$ N/A

After power up, PG is pulled low initially. The device initiates an inrush sequence in which the gate driver circuit starts charging the gate capacitance from the internal charge pump. When the FET gate voltage reaches the full overdrive indicating that the inrush sequence is complete and the device is capable of delivering full power, the PG pin is asserted HIGH after a de-glitch time ( $t_{PGA}$ ).

The PG is de-asserted if the FET is turned off at any time during normal operation. The PG de-assertion de-glitch time is  $t_{PGD}$ .



**Figure 7-7. TPS1685x PG Timing Diagram**

The PG is an open-drain pin and must be pulled up to an external supply.

When there is no supply to the device, the PG pin is expected to stay low. However, there is no active pulldown in this condition to drive this pin all the way down to 0V. If the PG pin is pulled up to an independent supply which is present even if the device is unpowered, there can be a small voltage seen on this pin depending on the pin sink current, which is a function of the pullup supply voltage and resistor. Minimize the sink current to keep this pin voltage low enough not to be detected as a logic HIGH by associated external circuits in this condition.

When the device is used in secondary mode (MODE = GND) in conjunction with another TPS1685x device as a primary device in a parallel chain, the secondary device controls the PG assertion during start-up. After the device reaches steady-state, the secondary device no longer has control over the PG de-assertion. Refer to the [Mode Selection \(MODE\)](#) for more details.

### 7.3.13 Output Discharge

The device has an integrated output discharge function which discharges the capacitors on the OUT pin using an internal constant current ( $I_{QOD}$ ) to GND. The output discharge function is activated when the EN/UVLO is held low ( $V_{SD(F)} < V_{EN} < V_{UVLO(F)}$ ) for a minimum interval ( $t_{QOD}$ ). The output discharge function helps to rapidly remove the residual charge left on large output capacitors and prevents the bus from staying at some undefined voltage for extended periods of time. The output discharge is disengaged when  $V_{OUT} < V_{FB}$  or if the device detects a fault.

The output discharge function can result in excessive power dissipation inside the device leading to an increase in junction temperature ( $T_J$ ). The output discharge is disabled if the junction temperature ( $T_J$ ) crosses TSD to avoid long-term degradation of the part.

#### Note

In a primary+secondary parallel configuration, TI recommends to hold EN/UVLO voltage below the  $V_{UVLO(F)}$  threshold of the secondary device to activate output discharge for all the devices in the chain.

### 7.3.14 FET Health Monitoring

The TPS1685x can detect and report certain conditions which are indicative of a failure of the power path FET. If undetected or unreported, these conditions can compromise system performance by not providing power to the load correctly or by not providing the necessary level of protection. After a FET failure is detected, the TPS1685x tries to turn off the internal FET by pulling the gate low and asserts the  $\overline{FLT}$  pin.

- **D-S short:** D-S short can result in a constant uncontrolled power delivery path formed from source to load, either due to a board assembly defect or due to internal FET failure. This condition is detected at start-up by checking if  $V_{IN-OUT} < V_{DSFLT}$  before the FET is turned ON. If yes, the device engages the internal output discharge to try and discharge the output. If the  $V_{OUT}$  does not discharge below  $V_{FB}$  within a certain allowed interval, the device asserts the  $\overline{FLT}$  pin.
- **G-D short:** The TPS1685x detects this kind of FET failure at all times by checking if the gate voltage is close to  $V_{IN}$  even when the internal control logic is trying to hold the FET in OFF condition.
- **G-S short:** The TPS1685x detects this kind of FET failure during start-up by checking if the FET G-S voltage fails to reach the necessary overdrive voltage within a certain timeout period ( $t_{SU\_TMR}$ ) after the gate driver is turned ON. While in steady-state, if the G-S voltage becomes low before the controller logic has signaled to the gate driver to turn off the FET, this action is latched as a fault.

### 7.3.15 Single Point Failure Mitigation

The TPS1685x relies on the proper component connections and biasing on the IMON, IREF, and ITIMER pins to provide overcurrent and short-circuit protection under all circumstances. As an added safety measure, the device uses the following mechanisms to verify that the device provides some form of overcurrent protection even if any of these pins are not connected correctly in the system or the associated components have a failure in the field.

#### 7.3.15.1 IMON Pin Single Point Failure

- **IMON pin open:** In this case, the IMON pin voltage is internally pulled up to a higher voltage and exceeds the threshold ( $V_{IREF}$ ), causing the part to perform a circuit-breaker action even if there is no significant current flowing through the device.
- **IMON pin shorted to GND directly or through a very low resistance:** In this case, the IMON pin voltage is held at a low voltage and is not allowed to exceed the threshold ( $V_{IREF}$ ) even if there is significant current flowing through the device, thereby rendering the primary overcurrent protection mechanism ineffective. The device relies on an internal overcurrent sense mechanism to provide some protection as a backup. If the device detects that the backup current sense threshold ( $I_{OC\_BKP}$ ) is exceeded but at the same time the primary overcurrent detection on IMON pin fails, the pin triggers single point failure detection and latches a fault. The FET is turned off and the  $\overline{FLT}$  pin is asserted.

### 7.3.15.2 IREF Pin Single Point Failure

- **IREF pin open or forced to higher voltage:** In this case, the IREF pin ( $V_{IREF}$ ) is pulled up internally or externally to a voltage which is higher than the target value as per the recommended  $I_{OCP}$  or  $I_{LIM}$  calculations, preventing the primary circuit-breaker, active current limit, and short-circuit protection from getting triggered even if there is significant current flowing through the device. The device relies on an internal overcurrent detection mechanism to provide some protection as a backup. If the device detects that the backup overcurrent threshold is exceeded but at the same time the primary overcurrent or short-circuit detection on IMON pin fails, single point failure detection is triggered and latches a fault. The FET is turned off and the  $\overline{FLT}$  pin is asserted.
- **IREF pin shorted to GND:** In this case, the  $V_{IREF}$  threshold is set to 0V, causing the part to perform active current limit or circuit-breaker action even if there is no significant current flowing through the device.

### 7.3.15.3 ITIMER Pin Single Point Failure

- **ITIMER pin open or short to GND:** In this case, the ITIMER pin is already discharged below  $V_{ITIMERTHR}$  and hence indicates overcurrent blanking timer expiry instantaneously after an overcurrent event and triggers a circuit-breaker action without any delay.
- **ITIMER pin forced to some voltage higher than  $V_{ITIMERTHR}$ :** In this case, the ITIMER pin is unable to discharge below  $V_{ITIMERTHR}$  and hence fails to indicate overcurrent blanking timer expiry, thereby rendering the circuit-breaker mechanism ineffective. The device relies on a backup overcurrent timer mechanism to provide some protection as a backup. If the device detects an overcurrent event on either the IMON pin or the backup overcurrent detection circuit, the device engages the internal backup time and after the timer expires ( $t_{SPFLTMR}$ ), latches a fault. The FET is turned off and the  $\overline{FLT}$  pin is asserted.

## 7.4 Device Functional Modes

The features of the device depend on the operating mode. [Table 7-6](#) and [Table 7-7](#) summarize the device functional modes.

**Table 7-6. Device Functional Modes Based on EN/UVLO Pin**

Pin: EN/UVLO	Device State	Output Discharge
$> V_{UVLO(R)}$	Fully ON	Disabled
$> V_{SD(F)}, < V_{UVLO(F)} (< t_{QOD})$	FET OFF	Disabled
$> V_{SD(F)}, < V_{UVLO(F)} (> t_{QOD})$	FET OFF	Enabled
$< V_{SD(F)}$	Shutdown	Disabled

**Table 7-7. Device Functional Modes Based on MODE Pin**

Pin: MODE	Device Configuration
Open	Primary or standalone
GND	Secondary

**Table 7-8. Device Functional Modes Based on Resistor at SFT\_SEL Pin**

$I_{SFT\_SEL}$	SFT_SEL pin	MODE pin
$I_{OC\_BKP}$	$R_{SFT\_SEL} < 95\text{k}\Omega$	Open
$2.5 \times I_{OCP}$	$105\text{k}\Omega < R_{SFT\_SEL} < 195\text{k}\Omega$	Open
$2.8 \times I_{OCP}$	$105\text{k}\Omega < R_{SFT\_SEL} < 195\text{k}\Omega$	GND
$2 \times I_{OCP}$	$205\text{k}\Omega < R_{SFT\_SEL} < 295\text{k}\Omega$	Open
$2.26 \times I_{OCP}$	$205\text{k}\Omega < R_{SFT\_SEL} < 295\text{k}\Omega$	GND
$1.5 \times I_{OCP}$	$305\text{k}\Omega < R_{SFT\_SEL}$	Open
$1.71 \times I_{OCP}$	$305\text{k}\Omega < R_{SFT\_SEL}$	GND

## 8 Application and Implementation

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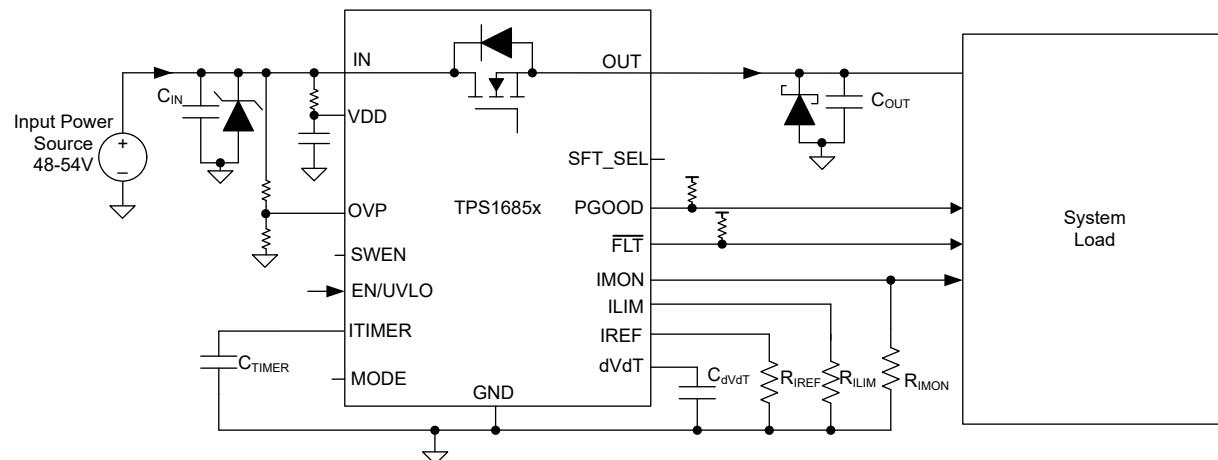
### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

The TPS1685x is a high voltage and current eFuse that is typically used for power rail protection applications. The device operates from 9V to 80V with input overvoltage and adjustable undervoltage protection. The device provides ability to control inrush current and offers protection against overcurrent and short-circuit conditions. The device can be used in a variety of systems such as server motherboards, add-on cards, graphics cards, accelerator cards, enterprise switches, routers, and so forth. The design procedure explained in the subsequent sections can be used to select the supporting component values based on the application requirements. Additionally, a spreadsheet design tool, [TPS1685x Design Calculator](#) is available in the web product folder.

#### 8.1.1 Single Device, Standalone Operation



**Figure 8-1. Single Device, Standalone Operation**

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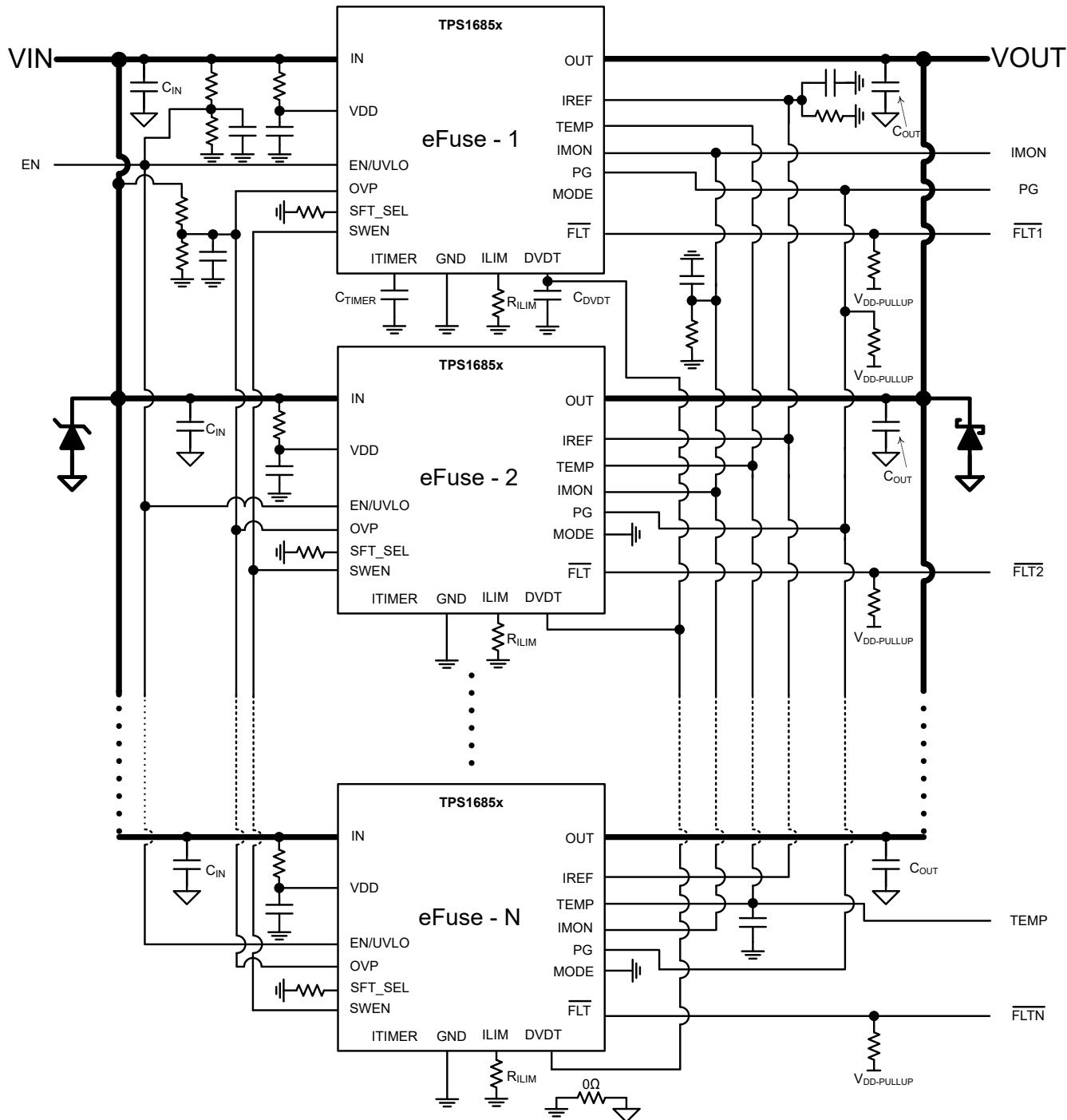
### Note

The MODE pin is left OPEN to configure for standalone operation.

#### Other variations:

1. The IREF pin can be driven from an external reference voltage source.
2. In a host MCU controlled system, EN/UVLO can be connected to a GPIO pin to control the device. IMON pin voltage can be monitored using an ADC. The host MCU can use a DAC to drive IREF to change the current limit threshold dynamically.
3. The device can be used as a simple high current load switch without adjustable overcurrent or fast-trip protection by tying the ILIM and IMON pins to GND and leaving the IREF pin open. The inrush current protection, fixed fast-trip and internal fixed overcurrent protection are still active in this condition.

### 8.1.2 Multiple Devices, Parallel Connection



**Figure 8-2. Devices Connected in Parallel for Higher Current Capability**

In this configuration, one TPS1685x device is designated as the primary device and controls the other TPS1685x devices in the chain which are designated as secondary devices. This configuration is achieved by connecting the primary device as follows:

1. VDD is connected to IN through an R-C filter.
2. MODE pin is left OPEN.
3. ITIMER is connected through capacitor to GND.

4. DVDT is connected through capacitor to GND.
5. IREF is connected through resistor to GND.
6. IMON is connected through resistor to GND.
7. ILIM is connected through resistor to GND.
8. SWEN is pulled up to a 3.3V to 5V standby rail. This rail must be powered up independent of the eFuse.

The secondary devices must be connected in the following manner:

1. VDD is connected to IN through a R-C filter.
2. MODE pin is connected to GND.
3. ITIMER pin is left OPEN.
4. ILIM is connected through resistor to GND.

The following pins of all devices must be connected together:

1. IN
2. OUT
3. EN/UVLO
4. OVP
5. DVDT
6. SWEN
7. PG
8. IMON
9. IREF

In this configuration, all the devices are powered up and enabled simultaneously.

**Power up:** After power up or enable, all devices initially hold the SWEN low till the internal blocks are biased and initialized correctly. After that, each device releases a dedicated SWEN. After all devices have released the SWEN, the combined SWEN goes high and the devices are ready to turn on the respective FETs at the same time.

**Inrush:** During inrush, because the DVDT pins are tied together to a single DVDT capacitor all the devices turn on the output with the same slew rate (SR). Choose the common DVDT capacitor ( $C_{DVDT}$ ) as per the following [Equation 14](#) and [Equation 15](#).

$$SR(V/ms) = \frac{I_{INRUSH}(A)}{C_{LOAD}(mF)} \quad (14)$$

$$C_{DVDT}(nF) = \frac{48}{SR(V/ms)} \quad (15)$$

In this condition, the internal balancing circuit verifies that the load current is shared among all devices during start-up. This action prevents a situation where some devices turn on faster than others and experience more thermal stress as compared to other devices. This can potentially result in premature or partial shutdown of the parallel chain, or even SOA damage to the devices. The current balancing scheme provides the inrush capability of the chain scales according to the number of devices connected in parallel, thereby verifying successful start-up with larger output capacitances or higher loading during start-up.

All devices hold the respective PG signals low during start-up. After the output ramps up fully and reaches steady-state, each device releases a dedicated PG pulldown. Because the DVDT pins of all devices are tied together, the internal gate high detection of all devices is synchronized. There can be some threshold or timing mismatches between devices leading to PG assertion in a staggered manner. However, since the PG pins of all devices are tied together, the combined PG signal becomes high only after all devices have released the PG pulldown. This signal is sent to the downstream loads to allow power to be drawn.

**Steady-state:** During steady-state, all devices share current equally using the active current sharing mechanism which actively regulates the respective device  $R_{DS0N}$  to evenly distribute current across all the devices in the parallel chain.

**Overcurrent during steady-state:** The circuit-breaker threshold for the parallel chain is based on the total system current rather than the current flowing through individual devices. This is done by connecting the IMON pins of all the devices together. Similarly, the IREF pins of all devices are tied together and connected to a single  $R_{IREF}$  (or an external  $V_{IREF}$  source) to generate a common reference for the overcurrent protection block in all the devices. This action helps minimize the contribution of  $I_{IREF}$  variation and  $R_{IREF}$  tolerance to the overall mismatch in overcurrent threshold between devices. In this case, choose the combined  $R_{IMON}$  as per the following [Equation 16](#):

$$R_{IMON} = \frac{I_{IREF} \times R_{IREF}}{G_{IMON} \times I_{OCP(TOTAL)}} \quad (16)$$

The  $R_{ILIM}$  value for each individual eFuse must be selected based on the following [Equation 17](#).

$$R_{ILIM} = \frac{1.1 \times N \times R_{IMON}}{3} \quad (17)$$

Where  $N$  = number of devices in parallel chain.

**Other variations:**

The IREF pin can be driven from an external voltage reference ( $V_{IREF}$ ).

$$R_{IMON} = \frac{V_{IREF}}{G_{IMON} \times I_{OCP(TOTAL)}} \quad (18)$$

During an overcurrent event, the overcurrent detection of all the devices is triggered simultaneously. This in turn triggers the overcurrent blanking timer (ITIMER) on each device. However, only the primary device uses the ITIMER expiry event as a trigger to pull the SWEN low for all the devices, thereby initiating the circuit-breaker action for the whole chain. This mechanism verifies that the mismatches in the current distribution, overcurrent thresholds and ITIMER intervals among the devices do not degrade the accuracy of the circuit-breaker threshold of the complete parallel chain or the overcurrent blanking interval.

However, the secondary devices also start the backup overcurrent timer and can trigger the shutdown of the whole chain if the primary device fails to do so within a certain interval.

**Severe overcurrent (short-circuit):** If there is a severe fault at the output (for example, output shorted to ground with a low impedance path) during steady-state operation, the current builds up rapidly to a high value and triggers the fast-trip response in each device. The devices use two thresholds for fast-trip protection – a user-adjustable threshold  $I_{SFT}$  as well as a fixed threshold  $I_{FFT}$ . After the fast-trip, the devices enter into a latch-off fault condition till the device is power cycled or re-enabled or expires the auto-retry timer (only for auto-retry variants).

## 8.2 Typical Application: 54V Power Path Protection in Data Center Servers

This design example considers a 54V system operating voltage with a tolerance of  $\pm 10\%$ . The maximum steady-state load current is 80A. If the load current exceeds 85A, the eFuse circuit must allow transient overload currents up to a 3ms interval. For persistent overloads lasting longer than that, the eFuse circuit must break the circuit and then latch-off. The eFuse circuit must charge a bulk capacitance of 1mF. [Figure 8-3](#) shows the application schematic for this design example.

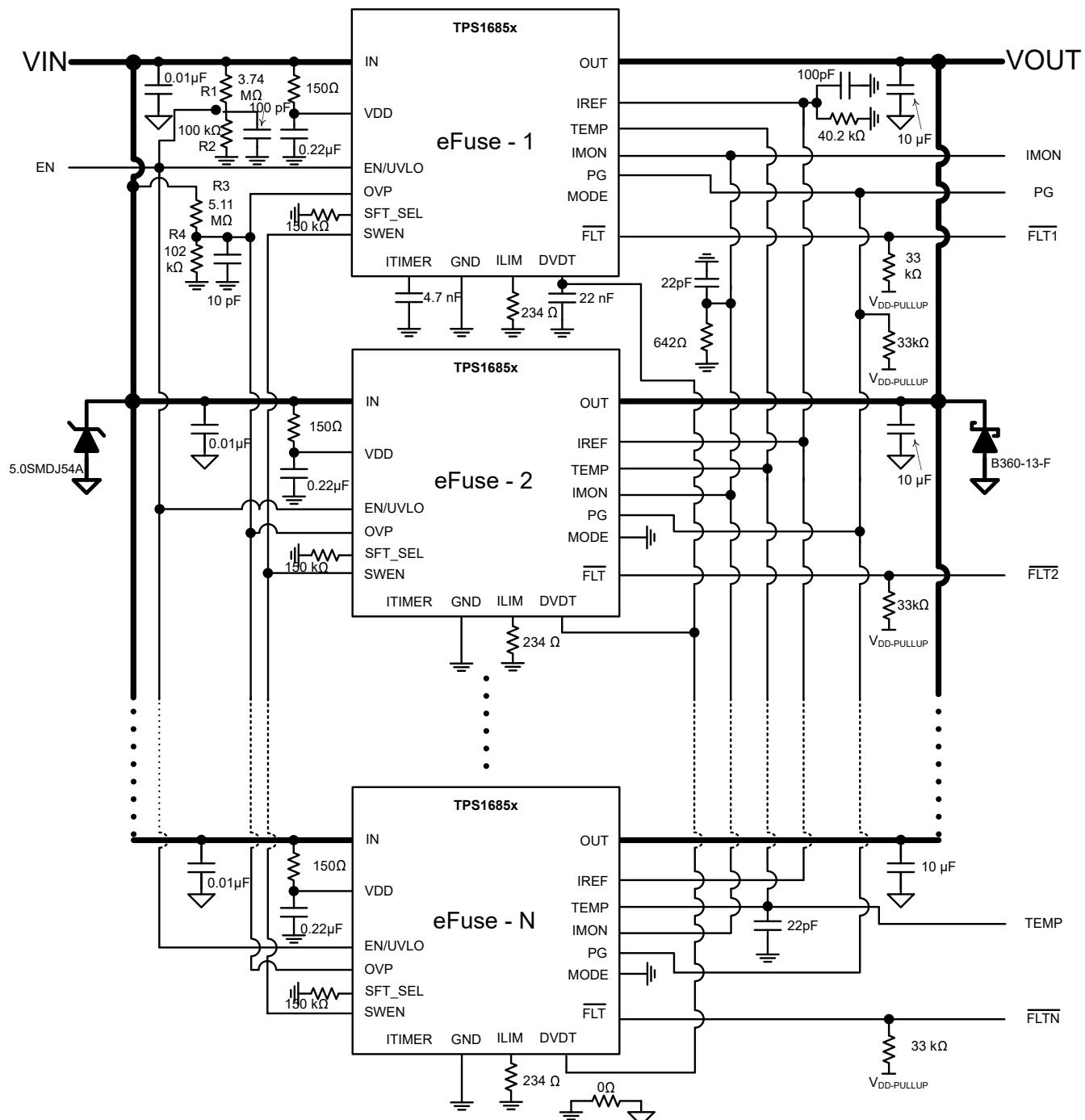


Figure 8-3. Application Schematic for a 54V, 4.3kW Power Path Protection Circuit

### 8.2.1 Design Requirements

Table 8-1 shows the design parameters for this application example.

**Table 8-1. Design Parameters**

PARAMETER	VALUE
Input voltage range ( $V_{IN}$ )	48.6V – 59.4V
Maximum DC load current ( $I_{OUT(max)}$ )	80A
Maximum output capacitance ( $C_{LOAD}$ )	1mF
Maximum ambient temperature	55°C
Transient overload blanking timer	3ms
Output voltage slew rate	2.2V/ms
Need to survive a “hot-short” on output condition ?	Yes
Need to survive a “power up into short” condition?	Yes
Can a board be hotplugged in or power cycled?	Yes
Load current monitoring needed?	Yes
Fault response	Latch-off

### 8.2.2 Detailed Design Procedure

- **Selecting the  $C_{DVDT}$  capacitor to control the output slew rate and start-up time**

A capacitor ( $C_{DVDT}$ ) must be added at the DVDT pin to GND to set the required value of slew rate. Equation 19 is used to compute the value of  $C_{DVDT}$ .

$$C_{DVDT}(nF) = \frac{50}{V_{IN}(V)/T_{SS}(ms)} \quad (19)$$

To get slew rate of 1V/ms, as per above equation we get  $C_{DVDT}$  as 50nF. Keep the nearby standard value of 47nF.

- **Selecting the  $R_{IREF}$  resistor to set the reference voltage for overcurrent protection.**

Equation 20 is used to calculate the value of  $R_{IREF}$ .

$$V_{IREF} = I_{IREF} \times R_{IREF} \quad (20)$$

In this design example,  $V_{IREF}$  is set at 1V. With  $I_{IREF} = 25\mu A$  (typical), calculate the target  $R_{IREF}$  to be 40k $\Omega$ . The closest standard value of  $R_{IREF}$  is 40.2k $\Omega$  with 0.1% tolerance and power rating of 100mW. For improved noise immunity, place a 100pF ceramic capacitor from the IREF pin to GND.

#### Note

Maintain  $V_{IREF}$  within the recommended voltage to verify the proper operation of overcurrent detection circuit.

#### Selecting the $R_{IMON}$ resistor to set the overcurrent (circuit-breaker) and fast-trip thresholds during steady-state

TPS1686x eFuse responds to the output overcurrent conditions during steady-state by turning off the output after a user-adjustable transient fault blanking interval. This eFuse continuously senses the total system current ( $I_{OUT}$ ) and produces a proportional analog current output ( $I_{IMON}$ ) on the IMON pin. This generates a voltage ( $V_{IMON}$ ) across the IMON pin resistor ( $R_{IMON}$ ) in response to the load current, which is defined as Equation 21.

$$V_{IMON} = I_{OUT} \times G_{IMON} \times R_{IMON} \quad (21)$$

$G_{IMON}$  is the current monitor gain ( $I_{IMON}$  :  $I_{OUT}$ ), whose typical value is  $18.2\mu\text{A}/\text{A}$ . The overcurrent condition is detected by comparing the  $V_{IMON}$  against the  $V_{IREF}$  as a threshold. The circuit-breaker threshold during steady-state ( $I_{OCP}$ ) can be calculated using [Equation 22](#).

$$I_{OCP} = \frac{V_{IREF}}{G_{IMON} \times R_{IMON}} \quad (22)$$

In this design example,  $I_{OCP}$  is considered as  $10\text{A}$ , and  $R_{IMON}$  can be calculated to be  $5.5\text{k}\Omega$  with  $G_{IMON}$  as  $18.2\mu\text{A}/\text{A}$  and  $V_{IREF}$  as  $1\text{V}$ . The nearest value of  $R_{IMON}$  is  $5.6\text{k}\Omega$  with  $0.1\%$  tolerance and power rating of  $100\text{mW}$ . For noise reduction, place a  $22\text{pF}$  ceramic capacitor across the IMON pin and GND.

- **Selecting the  $C_{ITIMER}$  capacitor to set the overcurrent blanking timer**

An appropriate capacitor must be connected at the ITIMER pin to ground of the primary or standalone device to adjust the duration for which the load transients above the circuit-breaker threshold are allowed. The transient overcurrent blanking interval can be calculated using [Equation 23](#).

$$t_{ITIMER}(\text{ms}) = \frac{C_{ITIMER}(\text{nF}) \times \Delta V_{ITIMER}(\text{V})}{I_{ITIMER}(\mu\text{A})} \quad (23)$$

Where  $t_{ITIMER}$  is the transient overcurrent blanking timer and  $C_{ITIMER}$  is the capacitor connected between ITIMER pin of the device and GND.  $I_{ITIMER} = 2\mu\text{A}$  (typical) and  $\Delta V_{ITIMER} = 1..55\text{V}$  (typical). A  $4.7\text{nF}$  capacitor with  $10\%$  tolerance and DC voltage rating of  $25\text{V}$  is used as the  $C_{ITIMER}$  for the device in this design.

- **Selecting the resistors to set the undervoltage lockout threshold**

The undervoltage lockout (UVLO) threshold is adjusted by employing the external voltage divider network of  $R_1$  and  $R_2$  connected between IN, EN/UVLO, and GND pins of the device as described in undervoltage protection section. The resistor values required for setting up the UVLO threshold are calculated using [Equation 24](#).

$$V_{IN(UV)} = V_{UVLO(R)} \frac{R_1 + R_2}{R_2} \quad (24)$$

To minimize the input current drawn from the power supply, TI recommends using higher resistance values for  $R_1$  and  $R_2$ . From the device electrical specifications, UVLO rising threshold  $V_{UVLO(R)} = 1.2\text{V}$ . From the design requirements,  $V_{INUVLO} = 46\text{V}$ . First choose the value of  $R_1 = 3.74\text{M}\Omega$  and use [Equation 24](#) to calculate  $R_2 = 100\text{k}\Omega$ . Use the closest standard  $1\%$  resistor values:  $R_1 = 3.74\text{M}\Omega$  and  $R_2 = 100\text{k}\Omega$ . For noise reduction, place a  $100\text{pF}$  ceramic capacitor across the EN/UVLO pin and GND.

- **Selecting the resistors to set the overvoltage lockout threshold**

The overvoltage lockout (OVLO) threshold is adjusted by employing the external voltage divider network of  $R_3$  and  $R_4$  connected between IN, OVLO, and GND pins of the device as described in the overvoltage protection section. The resistor values required for setting up the OVLO threshold are calculated using below equation.

$$V_{IN(OV)} = V_{OVLO(R)} \frac{R_3 + R_4}{R_4} \quad (25)$$

To minimize the input current drawn from the power supply, TI recommends using higher resistance values for  $R_3$  and  $R_4$ . From the device electrical specifications, OVLO rising threshold  $V_{OVLO(R)} = 1.17\text{V}$ . From the design requirements,  $V_{INOVLO} = 60\text{V}$ . First choose the value of  $R_1 = 5.11\text{M}\Omega$  and use [Equation 24](#) to calculate  $R_3 = 101\text{k}\Omega$ . Use the closest standard  $1\%$  resistor values:  $R_3 = 5.11\text{M}\Omega$  and  $R_4 = 102\text{k}\Omega$ . For noise reduction, place a  $10\text{pF}$  ceramic capacitor across the OVLO pin and GND.

- **Selecting the R-C filter between VIN and VDD**

VDD pin is intended to power the internal control circuitry of the eFuse with a filtered and stable supply, not affected by system transients. Therefore, use an R (150Ω) – C (0.22μF) filter from the input supply (IN pin) to the VDD pin. This helps to filter out the supply noises and to hold up the controller supply during severe faults such as short-circuit at the output. In a parallel chain, this R-C filter must be employed for each device.

- **Selecting the pullup resistors and power supplies for  $\overline{\text{FLT}}$ ,**

$\overline{\text{FLT}}$  is the open drain output. If these logic signal is used, the signal must be pulled up to an appropriate supply rail voltage through 33kΩ pullup resistances.

- **Selection of TVS diode at input and Schottky diode at output**

In the case of a short circuit and overload current limit when the device interrupts a large amount of current instantaneously, the input inductance generates a positive voltage spike on the input, whereas the output inductance creates a negative voltage spike on the output. The peak amplitudes of these voltage spikes (transients) are dependent on the value of inductance in series with the input or output of the device. Such transients can exceed the absolute maximum ratings of the device and eventually lead to failures due to electrical overstress (EOS) if appropriate steps are not taken to address this issue. Typical methods for addressing this issue include:

1. Minimize lead length and inductance into and out of the device.
2. Use a large PCB GND plane.
3. Addition of the Transient Voltage Suppressor (TVS) diodes to clamp the positive transient spike at the input.
4. Using Schottky diodes across the output to absorb negative spikes.

Refer to [TVS Clamping in Hot-Swap Circuits](#) , [Selecting TVS Diodes in Hot-Swap and ORing Applications](#), [TVS Diode recommendation tool](#) for details on selecting an appropriate TVS diode and the number of TVS diodes to be in parallel to effectively clamp the positive transients at the input below the absolute maximum ratings of the IN pin (90V). These TVS diodes also help to limit the transient voltage at the IN pin during the Hot Plug event. One(1) SMDJ54A is used in this design example.

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#### Note

Maximum Clamping Voltage  $V_C$  specification of the selected TVS diode at  $I_{pp}$  (10/1000μs) (V) must be lower than the absolute maximum rating of the power input (IN) pin for safe operation of the eFuse.

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Selection of the Schottky diodes must be based on the following criteria:

- The non-repetitive peak forward surge current ( $I_{FSM}$ ) of the selected diode must be more than the fast-trip threshold ( $2 \times I_{OCP(TOTAL)}$ ). Two or more Schottky diodes in parallel must be used if a single Schottky diode is unable to meet the required  $I_{FSM}$  rating. [Equation 26](#) calculates the number of Schottky diodes ( $N_{\text{Schottky}}$ ) that must be in parallel.

$$N_{\text{Schottky}} > \frac{2 \times I_{OCP(TOTAL)}}{I_{FSM}} \quad (26)$$

- Forward Voltage Drop ( $V_F$ ) at near to  $I_{FSM}$  must be as small as possible. The negative transient voltage at the OUT pin must be clamped within the absolute maximum rating of the OUT pin (-5V).
- DC Blocking Voltage ( $V_{RM}$ ) must be more than the maximum input operating voltage.
- Leakage current ( $I_R$ ) must be as small as possible.

1 B360-13-F is used in this design example.

- **Selecting  $C_{IN}$  and  $C_{OUT}$**

TI recommends to add ceramic bypass capacitors to help stabilize the voltages on the input and output. The value of  $C_{IN}$  must be kept small to minimize the current spike during hot-plug events. For each device, 0.01μF of  $C_{IN}$  is a reasonable target. Because  $C_{OUT}$  does not get charged during hot-plug, a larger value such as 10μF can be used at the OUT pin of each device.

### 8.2.3 Application Curves

All the waveforms below are captured on an evaluation setup with four TPS1685 eFuses in parallel. All the pullup supplies are derived from a separate standby rail.

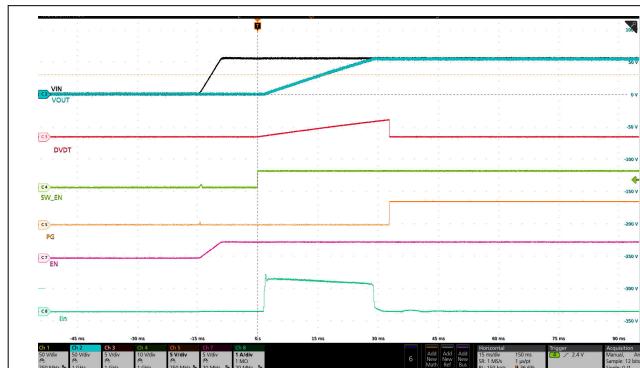


Figure 8-4.  $V_{IN}$  Ramped From 0V to 54V



Figure 8-5. Start-Up With EN/UVLO

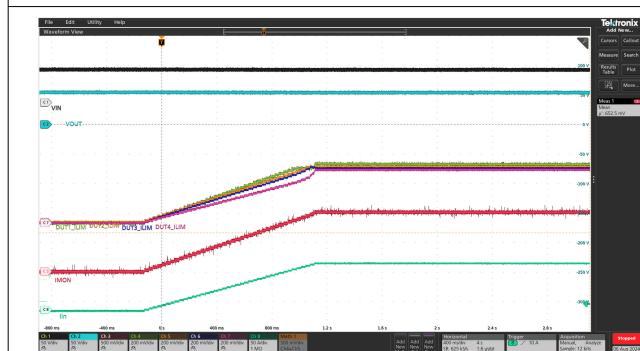


Figure 8-6. Active Current Sharing

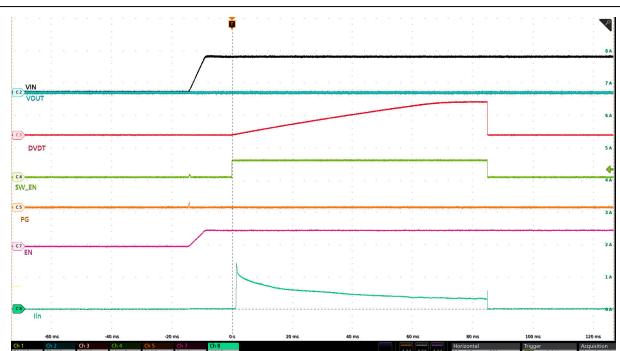


Figure 8-7. Power Up Into Short:  $V_{IN} = 54V$ , EN/UVLO Stepped Up From 0V to 3V

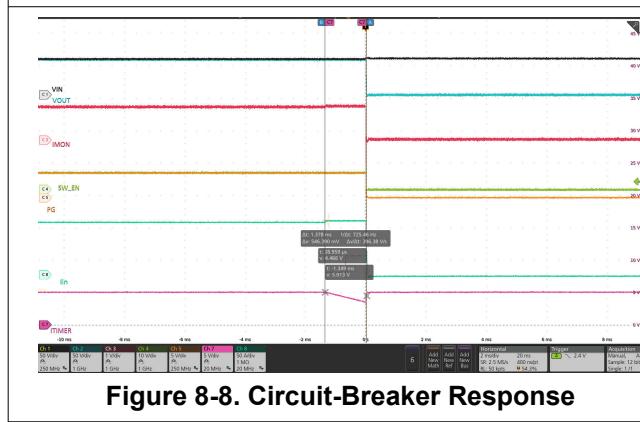


Figure 8-8. Circuit-Breaker Response

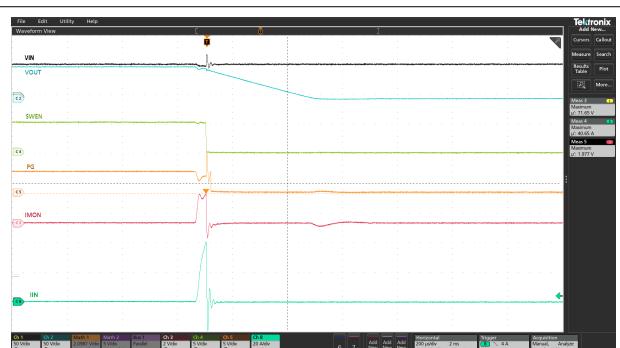


Figure 8-9. Output Hot-Short Response

### 8.3 Power Supply Recommendations

The TPS1685x devices are designed for a supply voltage in the range of 9V to 80V on the IN and VDD pins. TI recommends using a minimum capacitance of  $0.01\mu F$  on the IN pin of each device in parallel chain to avoid coupling of high slew rates during hot plug events. TI also recommends using an R-C filter from the input supply to the VDD pin on each device in parallel chain to filter out supply noise and to hold up the controller supply during severe faults such as short-circuit.

### 8.3.1 Transient Protection

In the case of a short-circuit or circuit-breaker event when the device interrupts current flow, the input inductance generates a positive voltage spike on the input, and the output inductance generates a negative voltage spike on the output. The peak amplitude of voltage spikes (transients) is dependent on the value of inductance in series to the input or output of the device. Such transients can exceed the absolute maximum ratings of the device if steps are not taken to address the issue. Typical methods for addressing transients include:

- Minimize lead length and inductance into and out of the device.
- Use a large PCB GND plane.
- Connect a Schottky diode from the OUT pin ground to absorb negative spikes.
- Connect a low ESR capacitor of  $10\mu\text{F}$  or higher at the OUT pin very close to the device.
- Connect a ceramic capacitor  $C_{IN} = 0.01\mu\text{F}$  or higher at the IN pin very close to the device to dampen the rise time of input transients. The capacitor voltage rating must be at least twice the input supply voltage to be able to withstand the positive voltage excursion during inductive ringing.

The approximate value of input capacitance can be estimated with [Equation 27](#).

$$V_{SPIKE(Absolute)} = V_{IN} + I_{LOAD} \times \sqrt{\frac{L_{IN}}{C_{IN}}} \quad (27)$$

where

$V_{IN}$  is the nominal supply voltage.

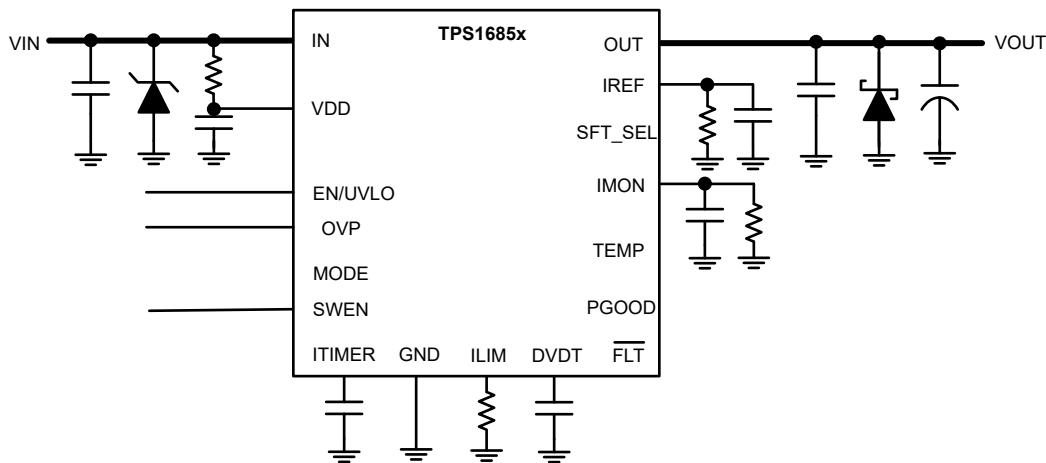
$I_{LOAD}$  is the load current.

$L_{IN}$  equals the effective inductance seen looking into the source.

$C_{IN}$  is the capacitance present at the input.

- Some applications can require the addition of a Transient Voltage Suppressor (TVS) to prevent transients from exceeding the absolute maximum ratings of the device. In some cases, even if the maximum amplitude of the transients is below the absolute maximum rating of the device, a TVS can help to absorb the excessive energy dump and prevent the device from creating very fast transient voltages on the input supply pin of the IC, which can couple to the internal control circuits and cause unexpected behavior.

The circuit implementation with optional protection components is shown in [Figure 8-10](#).



**Figure 8-10. Circuit Implementation with Optional Protection Components**

### 8.3.2 Output Short-Circuit Measurements

Obtaining repeatable and similar short-circuit testing results is difficult. The following contribute to variation in results:

- Source bypassing
- Input leads
- Circuit layout
- Component selection
- Output shorting method
- Relative location of the short
- Instrumentation

The actual short exhibits a certain degree of randomness because the short microscopically bounces and arcs. Verify that the configuration and methods are used to obtain realistic results. Do not expect to see waveforms exactly like those in this data sheet because every setup is different.

## 8.4 Layout

### 8.4.1 Layout Guidelines

- For all applications, TI recommends a ceramic decoupling capacitor of  $0.1\mu\text{F}$  or greater between the IN terminal and GND terminal.
- For all applications, TI recommends a ceramic decoupling capacitor of  $10\mu\text{F}$  or greater between the OUT terminal and GND terminal.
- The optimal placement of the decoupling capacitor is closest to the IN and GND terminals of the device. Care must be taken to minimize the loop area formed by the bypass-capacitor connection, the IN terminal, and the GND terminal of the IC. See the following figure for a PCB layout example.
- High current-carrying power-path connections must be as short as possible and must be sized to carry at least twice the full-load current.
- The GND terminal must be tied to the PCB ground plane at the terminal of the IC. The PCB ground must be a copper plane or island on the board.
- The IN and OUT pins are used for Heat Dissipation. Connect to as much copper area as possible with thermal vias.
- Locate the following support components close to the connection pins:
  - $R_{ILIM}$
  - $R_{IMON}$
  - $C_{IMON}$
  - $R_{IREF}$
  - $C_{IREF}$
  - $C_{dVdT}$
  - $C_{ITIMER}$
  - $C_{IN}$
  - $C_{OUT}$
  - $C_{VDD}$
  - Resistors for the EN/UVLO pin and OVP pin
- Connect the other end of the component to the GND pin of the device with shortest trace length. The trace routing for the  $C_{IN}$ ,  $C_{OUT}$ ,  $C_{VDD}$ ,  $R_{IREF}$ ,  $C_{IREF}$ ,  $R_{ILIM}$ ,  $R_{IMON}$ ,  $C_{IMON}$ ,  $C_{ITIMER}$  and  $C_{dVdT}$  components to the device must be as short as possible to reduce parasitic effects on the current limit, overcurrent blanking interval and soft-start timing. These traces must not have any coupling to switching signals on the board.
- Because the IMON, ILIM, IREF and ITIMER pins directly control the overcurrent protection behavior of the device, the PCB routing of these nodes must be kept away from any noisy (switching) signals.
- TI recommends to keep the parasitic loading on SWEN pin to a minimum to avoid synchronization issues.
- Protection devices such as TVS, snubbers, capacitors, or diodes must be placed physically close to the device the diodes are intended to protect. These protection devices must be routed with short traces to reduce inductance. For example, TI recommends a protection Schottky diode to address negative transients due to switching of inductive loads, and the diode must be physically close to the OUT pins.

### 8.4.2 Layout Example

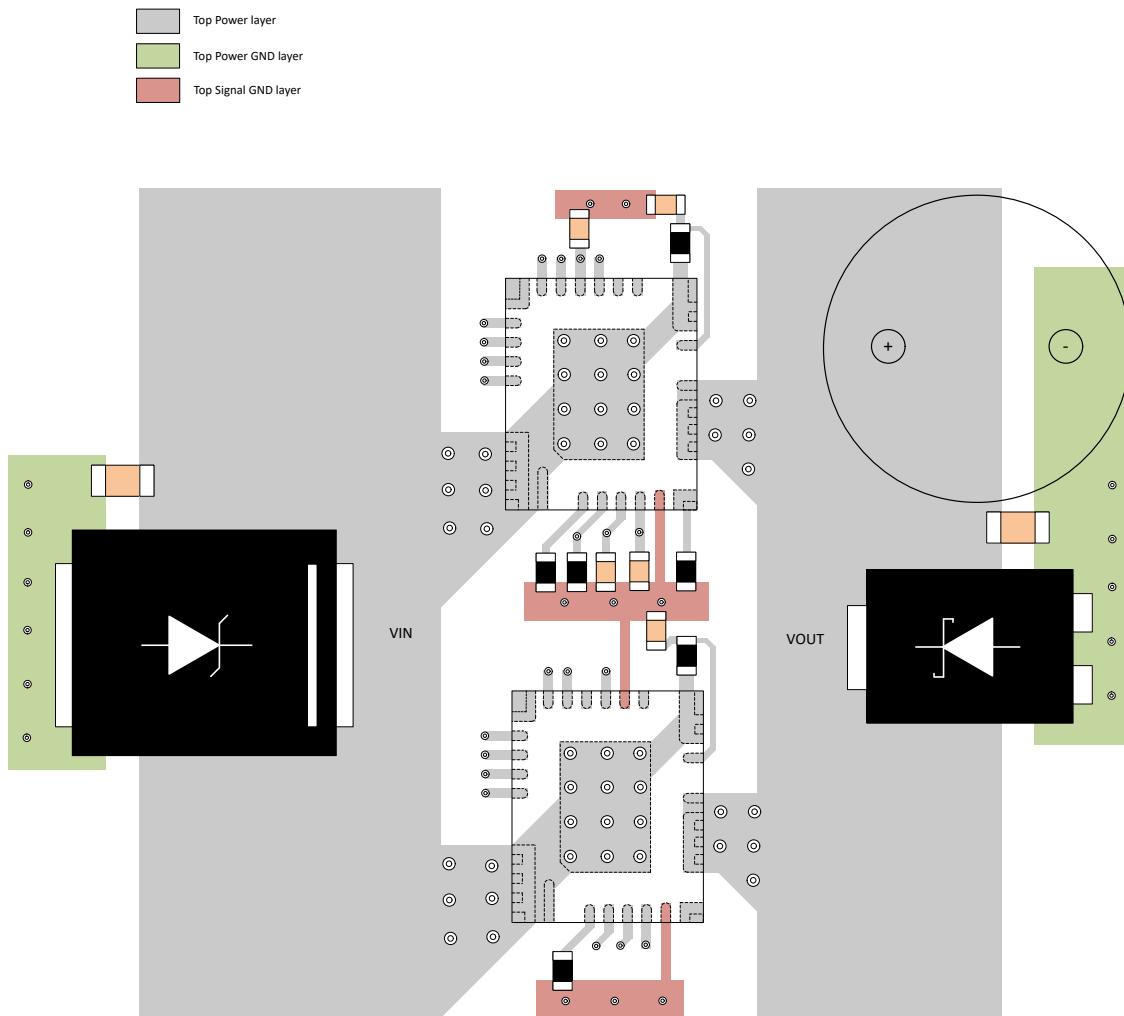


Figure 8-11. TPS1685x Two Parallel Devices Layout Example

## 9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [TPS1685EVM eFuse Evaluation Board](#)
- Texas Instruments, [TPS1685x Design Calculator](#)

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

### 9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision B (May 2025) to Revision C (August 2025)</b>	<b>Page</b>
• Added TPS1685xA OPN variant to the table.....	<a href="#">2</a>
• Changed $R_{ITMR}$ min from $7\Omega$ to $5\Omega$ in the Electrical Characteristics Section.....	<a href="#">7</a>
• Changed $I_{TIMER}$ max ratio from 0.78 to 0.97 in the Electrical Characteristics section.....	<a href="#">7</a>
• Changed $G_{IMON(ACS)}$ min from $18.02\mu\text{A}/\text{A}$ to $17.24\mu\text{A}/\text{A}$ in the Electrical Characteristics Section.....	<a href="#">7</a>
• Changed $G_{IMON(ACS)}$ max from $18.71\mu\text{A}/\text{A}$ to $19.84\mu\text{A}/\text{A}$ in the Electrical Characteristics Section.....	<a href="#">7</a>
• Updated $R_{ON(GHI)}$ typ value from $3.6\text{m}\Omega$ to $3.8\text{m}\Omega$ in the Electrical Characteristics Section.....	<a href="#">7</a>
• Changed Test condition from $V_{DS} > V_{DSCOMP}$ to $I_{OUT} \downarrow$ to $V_{DS} > V_{DSCOMP}$ to $SWEN \downarrow$ for $T_{FFT}$ Test in Timing Requirements Section .....	<a href="#">10</a>
• Changed typ of QOD enable time from 6ms to 16 $\mu\text{s}$ in Timing Characteristics Section .....	<a href="#">10</a>
• Changed typ data of $C_{dvdt} = 68\text{nF}$ to $C_{dvdt} = \text{open}$ .....	<a href="#">11</a>
• Fixed the Startup AOA graph by removing the DC label.....	<a href="#">12</a>

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<b>Changes from Revision A (April 2025) to Revision B (May 2025)</b>	<b>Page</b>
• Updated EN UVLO falling min from 1.1V to 1.0V in the Electrical Characteristics section.....	7
• Updated VOVP(R) min from 1.14V to 1.11V in the Electrical Characteristics section.....	7
• Changed $I_{\text{TIMER}}$ ratio min from 0.63 to 0.49 in the Electrical Characteristics section.....	7

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## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
PTPS16850VMAR.A	Active	Preproduction	LQFN-CLIP (VMA)   23	2500   LARGE T&R	-	Call TI	Call TI	-40 to 125	
PTPS16851VMAR.A	Active	Preproduction	LQFN-CLIP (VMA)   23	2500   LARGE T&R	-	Call TI	Call TI	-40 to 125	
<a href="#">TPS16850AVMAR</a>	Active	Production	LQFN-CLIP (VMA)   23	2500   LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T16850A
<a href="#">TPS16850VMAR</a>	Active	Production	LQFN-CLIP (VMA)   23	2500   LARGE T&R	-	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS16850
TPS16850VMAR.A	Active	Production	LQFN-CLIP (VMA)   23	2500   LARGE T&R	-	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS16850
TPS16850VMAR.B	Active	Production	LQFN-CLIP (VMA)   23	2500   LARGE T&R	-	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS16850
<a href="#">TPS16851AVMAR</a>	Active	Production	LQFN-CLIP (VMA)   23	2500   LARGE T&R	ROHS Exempt	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	T16851A
<a href="#">TPS16851VMAR</a>	Active	Production	LQFN-CLIP (VMA)   23	2500   LARGE T&R	-	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TPS16851

<sup>(1)</sup> **Status:** For more details on status, see our [product life cycle](#).

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

<sup>(4)</sup> **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

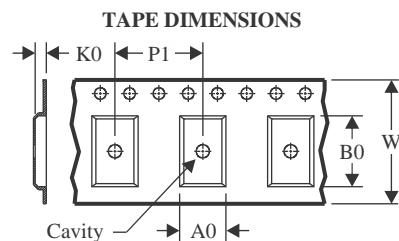
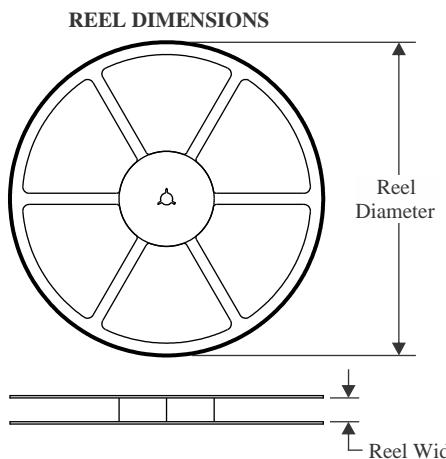
<sup>(5)</sup> **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

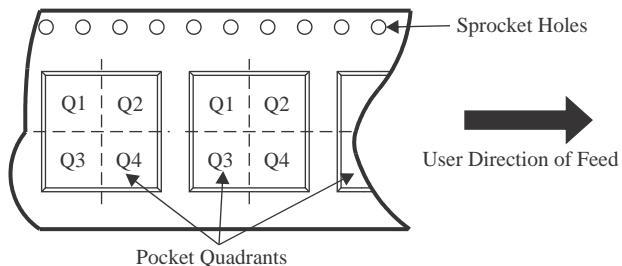
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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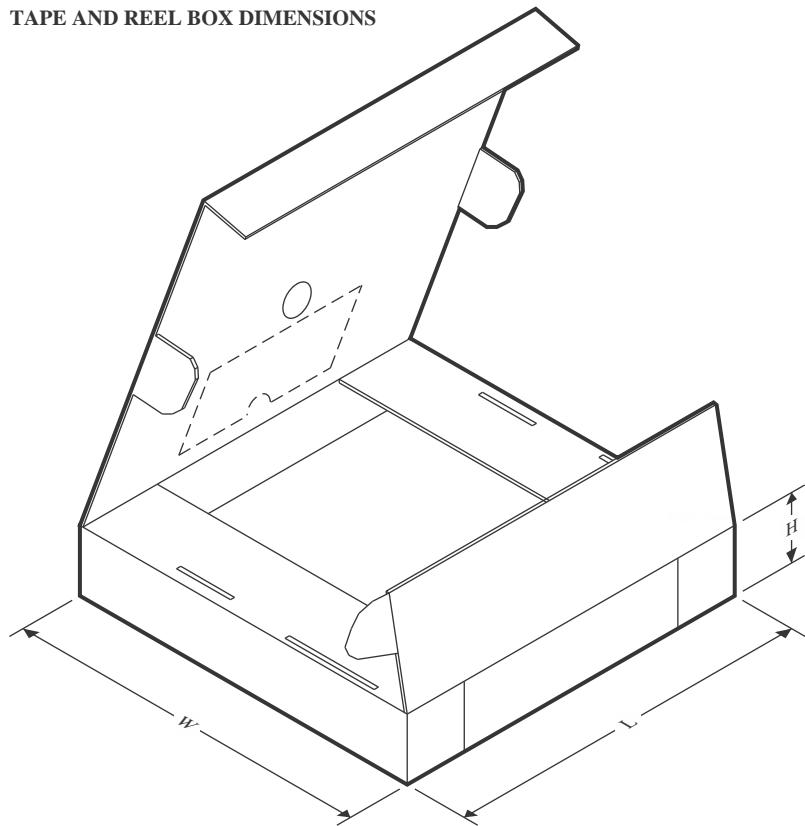
**TAPE AND REEL INFORMATION**


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS16850AVMAR	LQFN-CLIP	VMA	23	2500	330.0	16.4	6.3	5.3	1.75	8.0	16.0	Q1
TPS16850VMAR	LQFN-CLIP	VMA	23	2500	330.0	16.4	6.3	5.3	1.75	8.0	16.0	Q1
TPS16851AVMAR	LQFN-CLIP	VMA	23	2500	330.0	16.4	6.3	5.3	1.75	8.0	16.0	Q1
TPS16851VMAR	LQFN-CLIP	VMA	23	2500	330.0	16.4	6.3	5.3	1.75	8.0	16.0	Q1

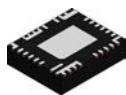
**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS16850AVMAR	LQFN-CLIP	VMA	23	2500	367.0	367.0	38.0
TPS16850VMAR	LQFN-CLIP	VMA	23	2500	367.0	367.0	38.0
TPS16851AVMAR	LQFN-CLIP	VMA	23	2500	367.0	367.0	38.0
TPS16851VMAR	LQFN-CLIP	VMA	23	2500	367.0	367.0	38.0

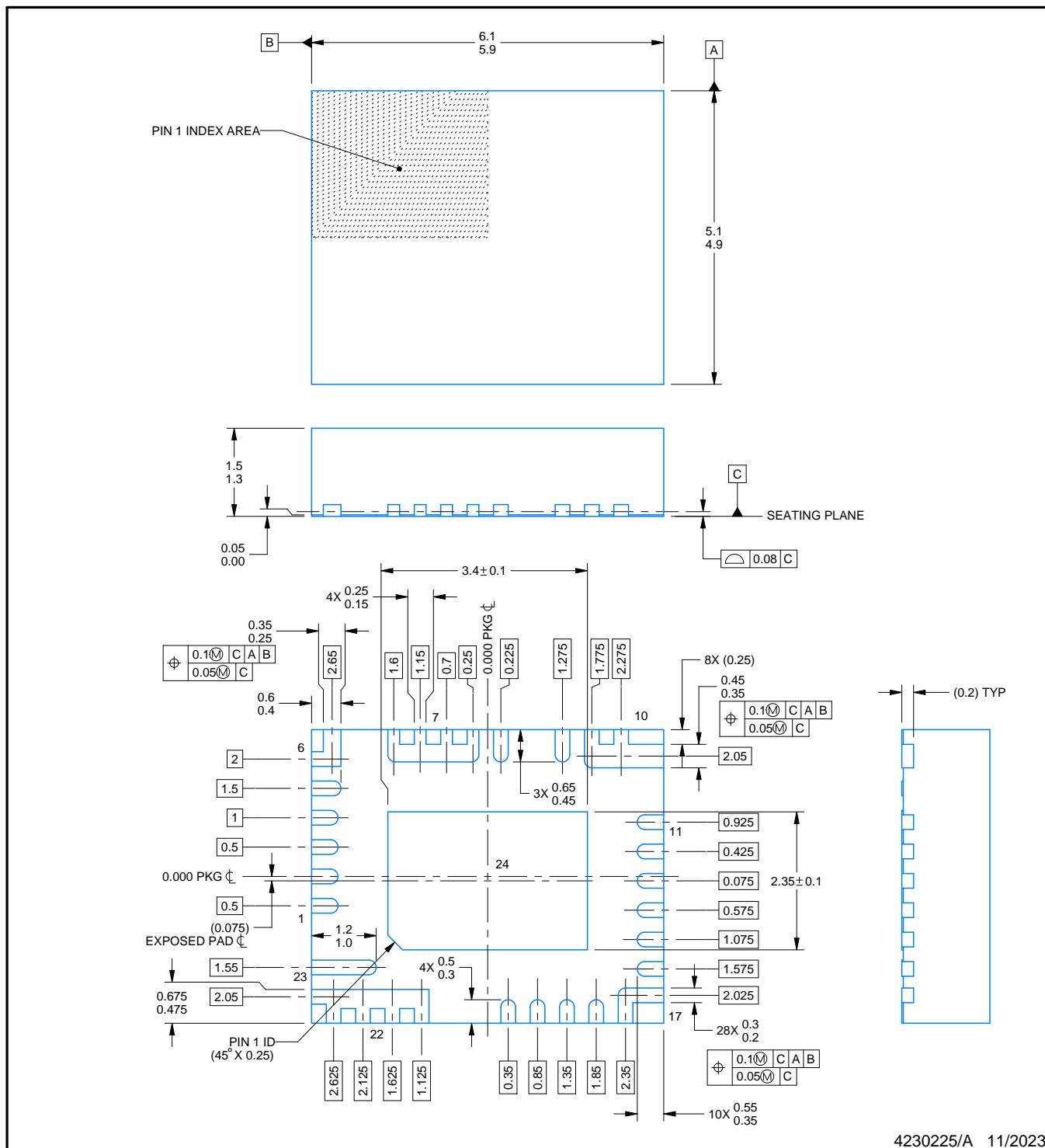
# PACKAGE OUTLINE

VMA0023A



LQFN-CLIP - 1.5 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4230225/A 11/2023

## NOTES:

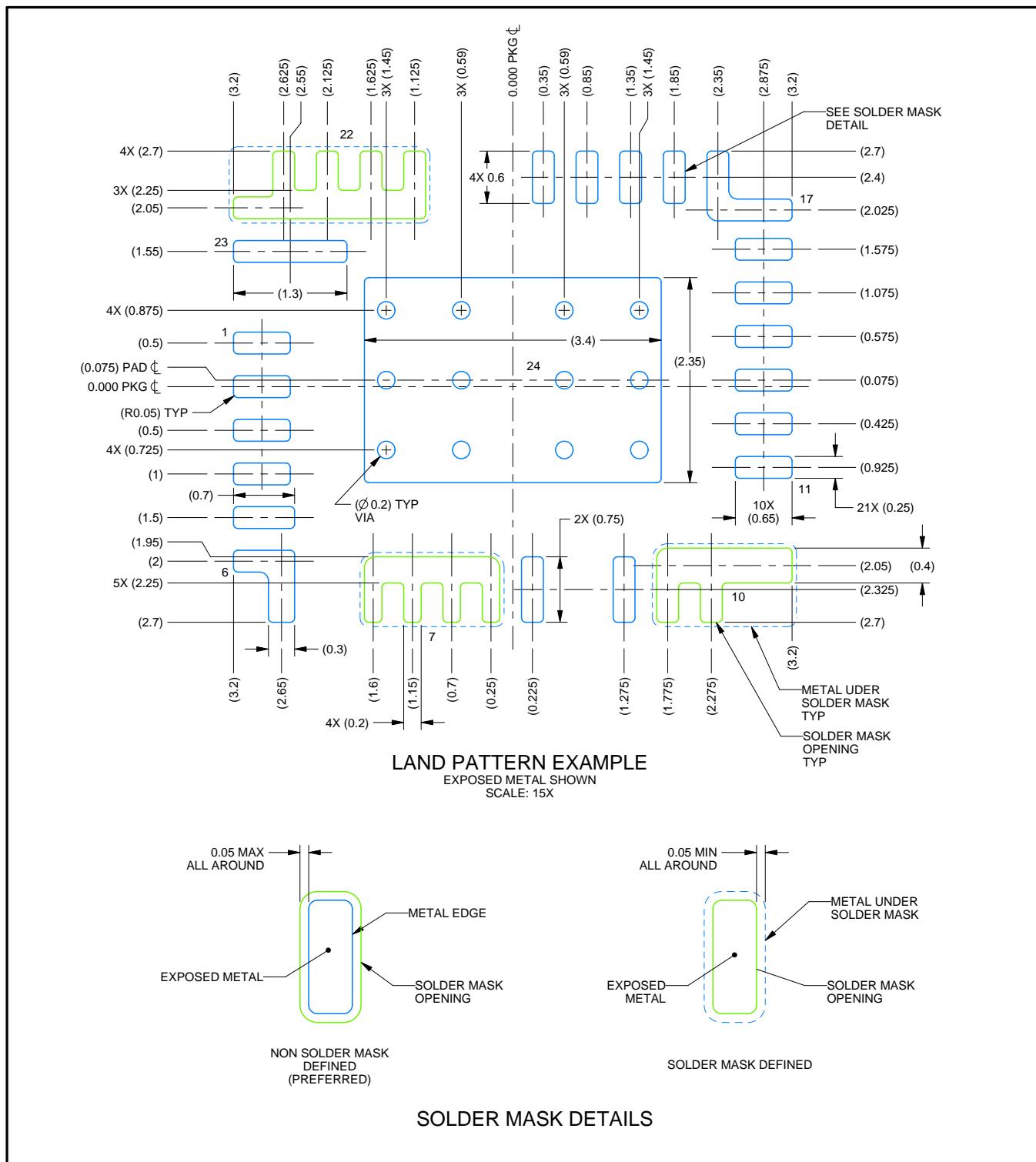
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

# EXAMPLE BOARD LAYOUT

VMA0023A

LQFN-CLIP - 1.5 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

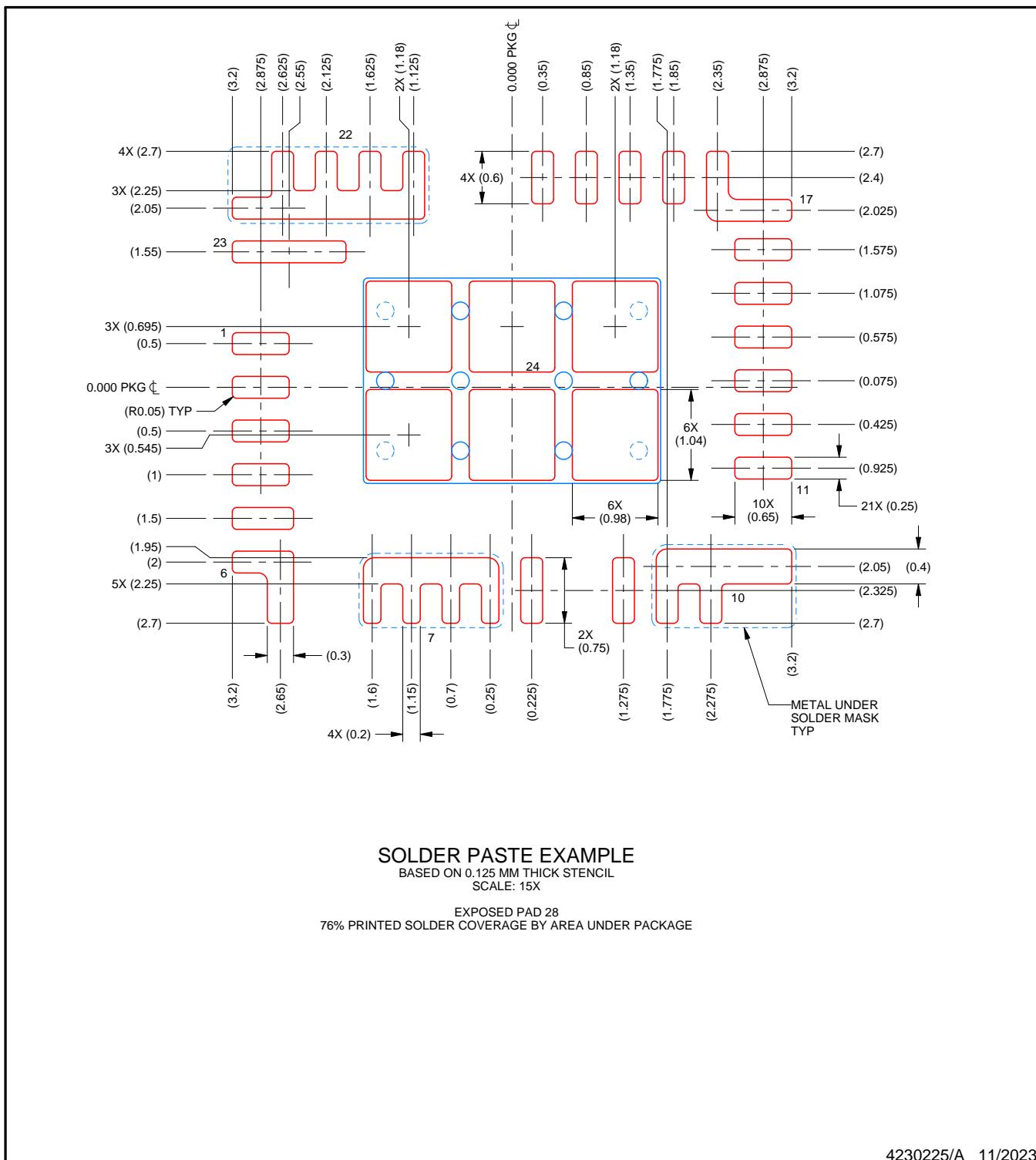
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

VMA0023A

LQFN-CLIP - 1.5 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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Last updated 10/2025